Analysis of SiW-ECAL technological prototype beam test with electron beam

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R&D of SiW-ECAL technological prototypes

## Major changes in FEV11 → 13 and SMBv4 → v5

- ➤ ASIC: SKIROC2 → 2A
  - – Individual threshold control
  - – Improvements on TDC

- ➤ Smaller SMB footprint

- ➤ Connection by 0.4mm-pitch flex cables
 - – Two candidates, footprint compatible

Flexible cable with Panasonic connector

Micro-coaxial cable by KEL

FEV11 & SMBv4

Al

FEV (PCB)

SMB

DIF

Wafer

ASU

Carbon sheet
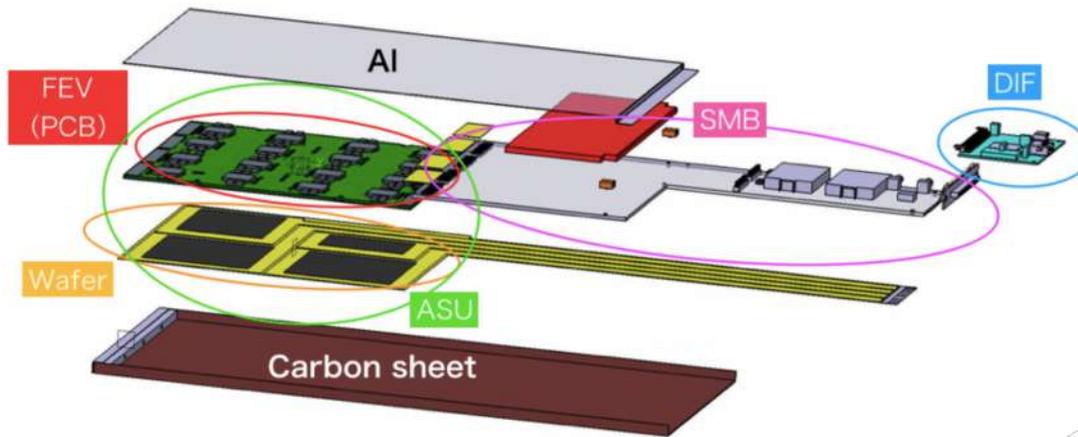
FEV13 & SMBv5
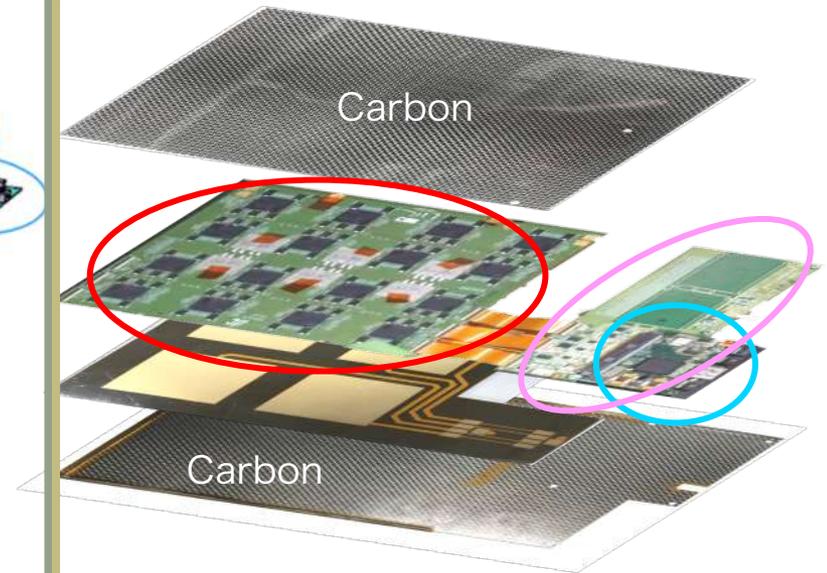
Carbon

Carbon

Analogue core: SKIROC2A

◦ Outputs: Gain (High/Low), TDC
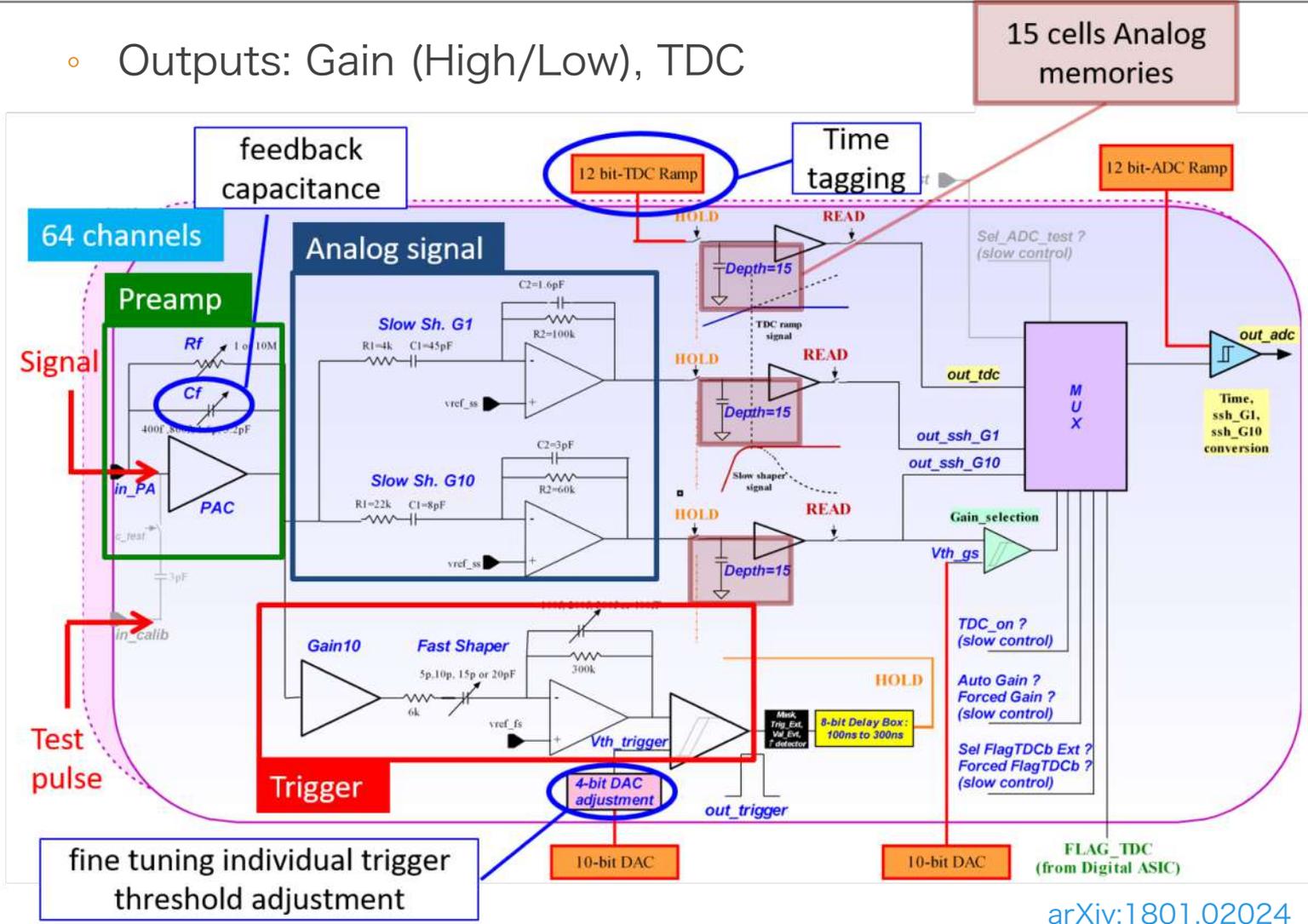
arXiv:1801.02024

FEV13-Jp Status

- ASIC: SKIROC2A
- Si thickness: 320μm & <u>650μm</u> New!
  ◦ 256 ch/sensor × 4 sensor/slab
- FEV-SMB Connection: Flexible cable or Micro-coaxial cable
- EM shielding: w/ Carbon frame and cover
- Power Pulsing

> ➤ See previous talk for details

Total 5 slabs
in Kyushu U., Japan

slab ID	P1	P2	P3	K1	K2
Si thickness	650 μm	650 μm	320 μm	650 μm	650 μm
Assembly	in Kyushu U.	in Kyushu U.	in Kyushu U.	in LLR	in Kyushu U.

Beam Test 2019 @ DESY

- Beam time:
  - 24th June - 7th July at DESY test beam facility
  - e⁻ beam: 1 - 5 GeV

- Presence from:

- Support & Hardware from:
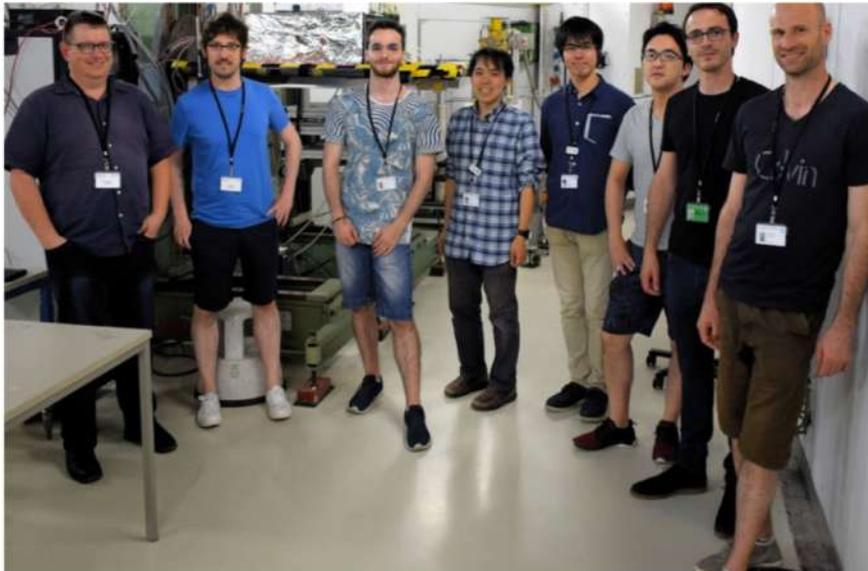
Beam Test 2019 @ DESY

- Beam time:
  - 24th June - 7th July at DESY test beam facility
  - e⁻ beam: 1 - 5 GeV

- Objectives:
  - Comparison of ASU based on BGA and based on Chip-On-Board (COB)
  - Test of new SL-Boards (SLB)
  - <u>Validation of FEV13-Jp</u> ← Target of this talk

- Programs:

<u>MIP program (w/o Tungsten)</u>
  - <u>Position scan for MIP calibration</u>
  - TDC test
  - Angled beam: 25 deg.
  - <u>Retriggering / double pedestal</u>

<u>Shower program (w/ Tungsten)</u>
  - <u>Energy measurement</u>
  - Response from large signal
  - TDC / auto gain
  - Edge effect

Setup for Beam Test

● Devices: 2 types of readouts
  ◦ DIF based slabs: FEV13-Jp × 5
  ◦ SLB based slabs:
    ◦ COB × 2
    ◦ FEV12 × 2

● Absorber: Tungsten
  ◦ X_0 = 3.5 mm, R_M = 9 mm, λ_0 = 96 mm

e⁻

■ SLB slabs ■ DIF slabs
■ Tungsten (2.1 mm / 4.2 mm)
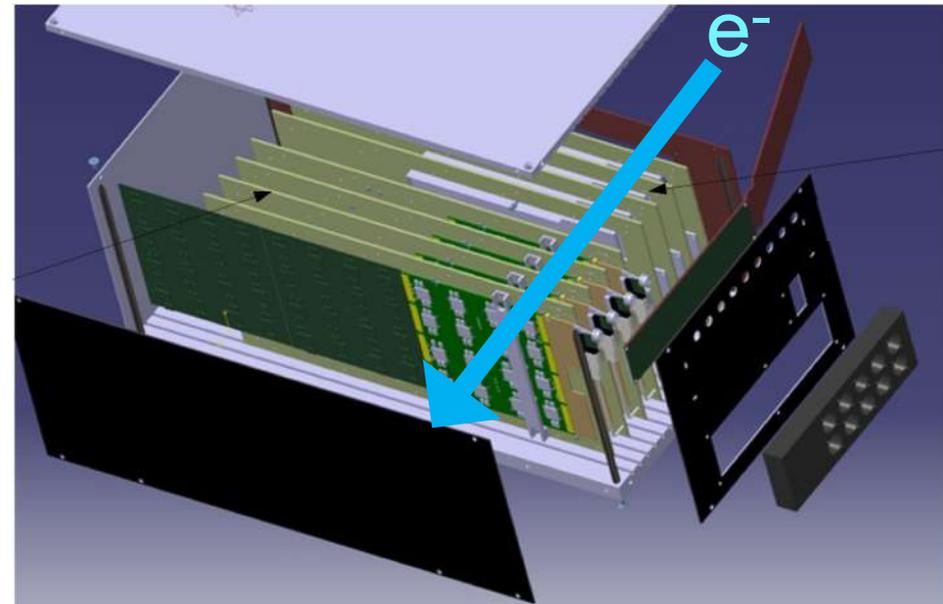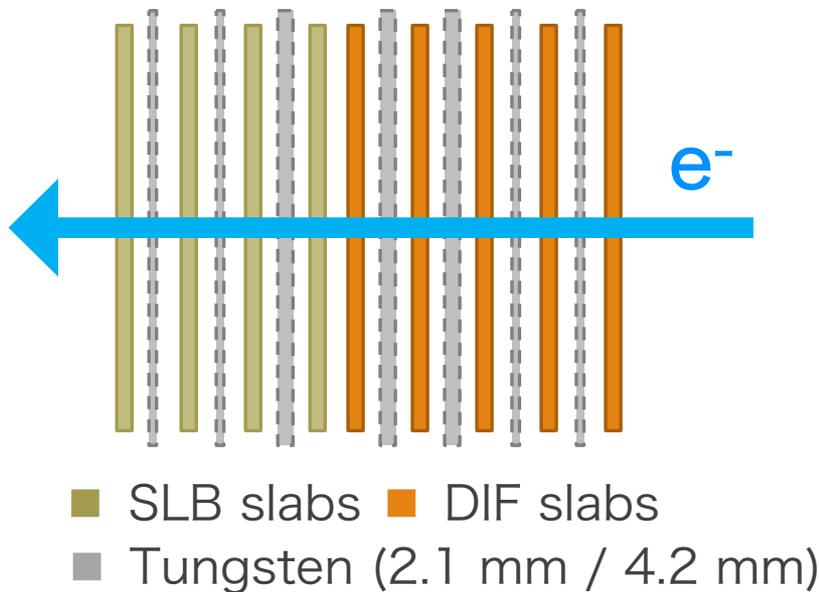
Procedure for Energy Measurement

Single Slab Analysis

1. Trigger adjustment & Masking of noisy channels
2. Pedestal calibration

   16 chips × 64 channels × 15 memories
3. Gain calibration using MIP

   16 chips × 64 channels

Multi Slab Analysis [in progress]

1. Timing coincidence

   using bunch crossing ID (BCID): Δt = 0.2 μs
2. Event Building

Trigger Adjustment

- Threshold scan is performed for estimation of S/N_{Trig} and trigger adjustment.

$$S/N_{Trig} \equiv \frac{\mu_{2\text{MIP}} - \mu_{1\text{MIP}}}{\sigma_{1\text{MIP}}}$$

- Test pulse of {4.2, 8.4} fC is injected.
  - 4.2 fC: 1 MIP for 320 μm

- S-curve is fitted by Err-function.

$$f(x) = A \times Erfc(\frac{x - \mu}{\sqrt{2}\sigma}) + const.$$

Injection [fC]	4.2	8.4
mean [DAC]	265.4	340.4
sigma [DAC]	12.0	12.5
S/N_{Trig}	6.4 ± 0.8	

- Trigger is set as 0.5 MIP of 320 μm slab: ~ 230 DAC.

S/N_{Trig} is worse (previous: 11.6), under investigation.

slabP1 chip12 ch58

S/N

S/N_{Trig} = 6.4 ± 0.8
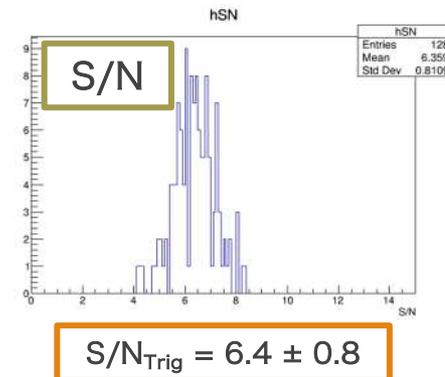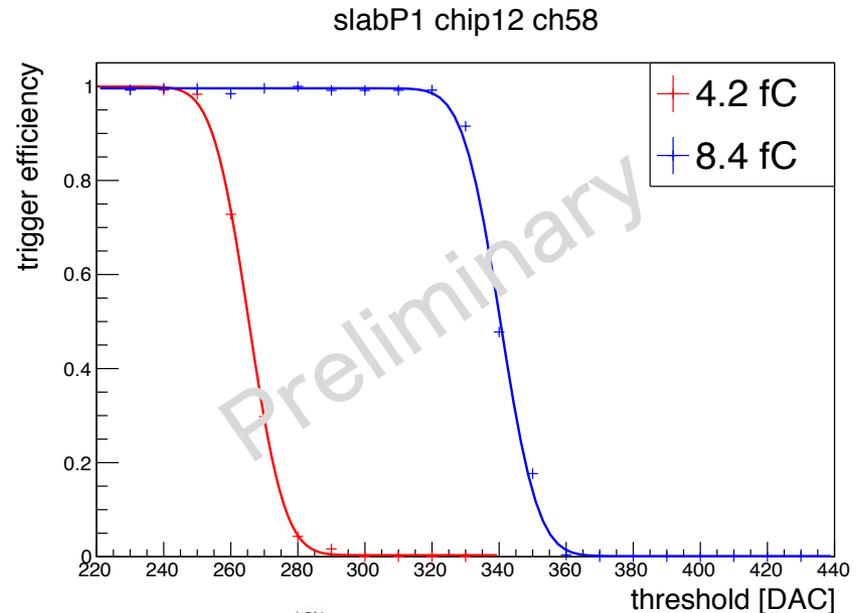
P1, all chips, ch 58-63

Trigger calib. (0.5MIP)
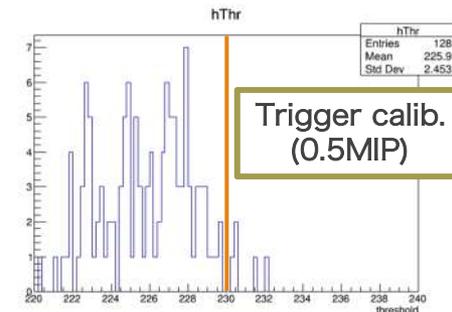
Masking of Noisy channels

- A few channels are noisy after trigger adjustment and masked: 1 - 2 %.
- Individual threshold control was not used because it wasn't ready. → Next TB
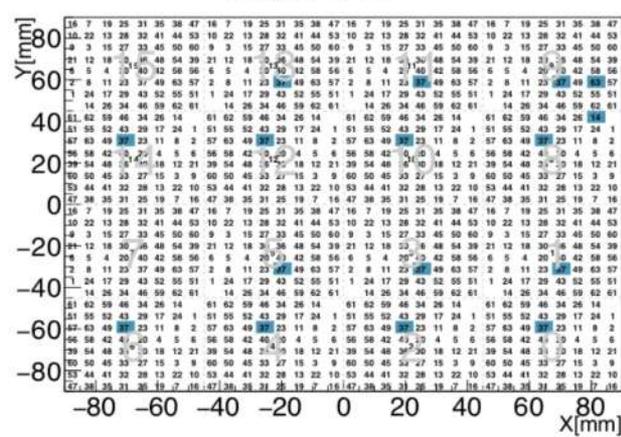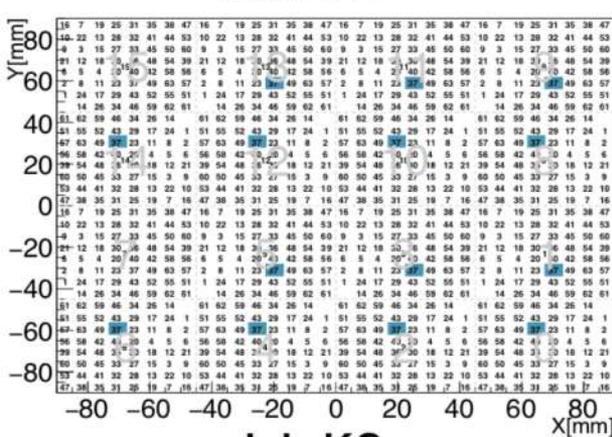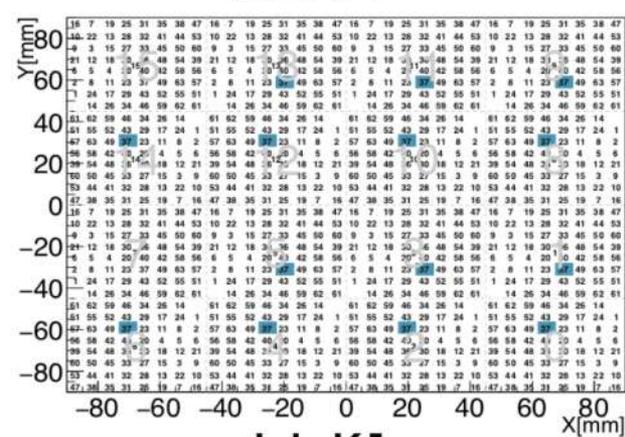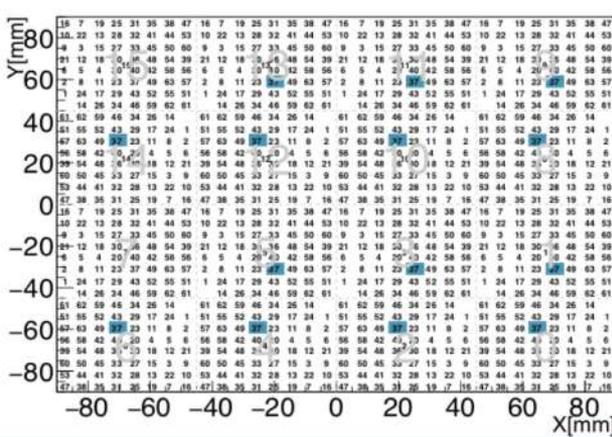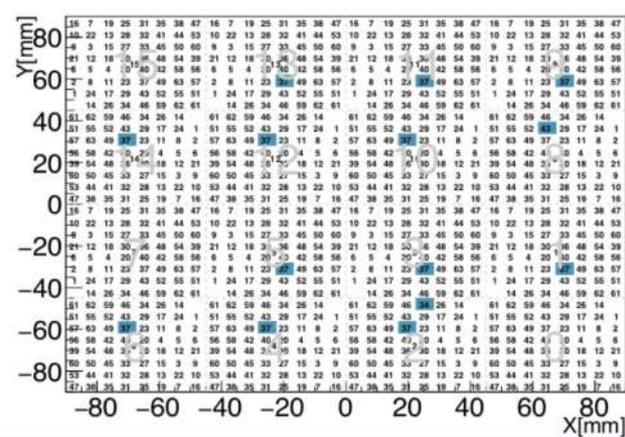
Pedestal Analysis

- Non-triggered ADC output (around ~300 [ADC])
- Fitted by Gaussian

lowGain[13][0][39] {lowGain[13][0][39]>250&&lowGain[13][0][39]<500&&badbcid[13][0]==0}

htemp	
Entries	5062
Mean	313.5
Std Dev	56.37
χ^2 / ndf	10.29 / 9
Constant	998.2 ± 18.6
Mean	289.8 ± 0.1
Sigma	3.393 ± 0.036

pedestal peak
(non-triggered)

MIP events
(triggered)

lowGain[13][0][39]
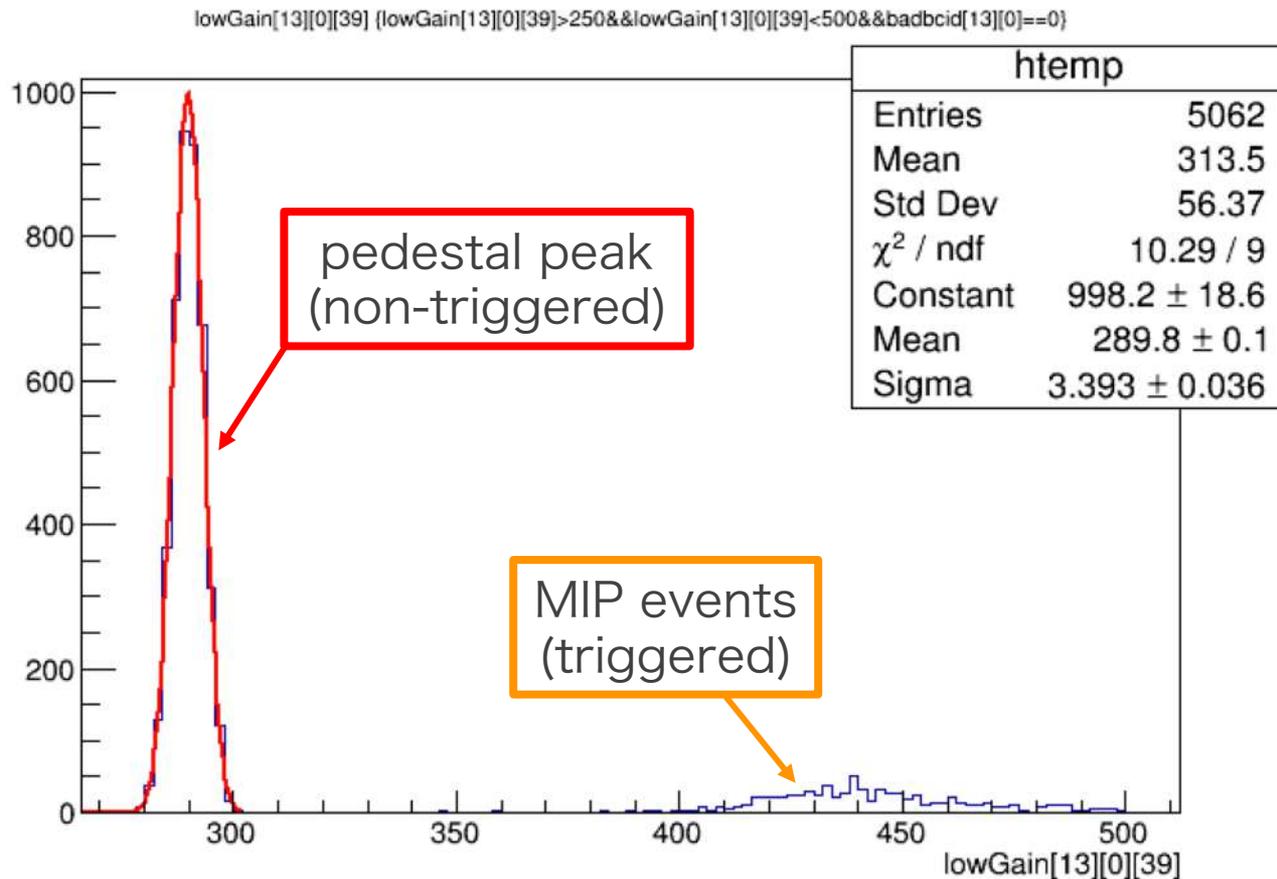
Pedestal Uniformity: Mean

- Mean of Gaussian
- Result of 1st Memory (Memory-cell dependence is referred later.)
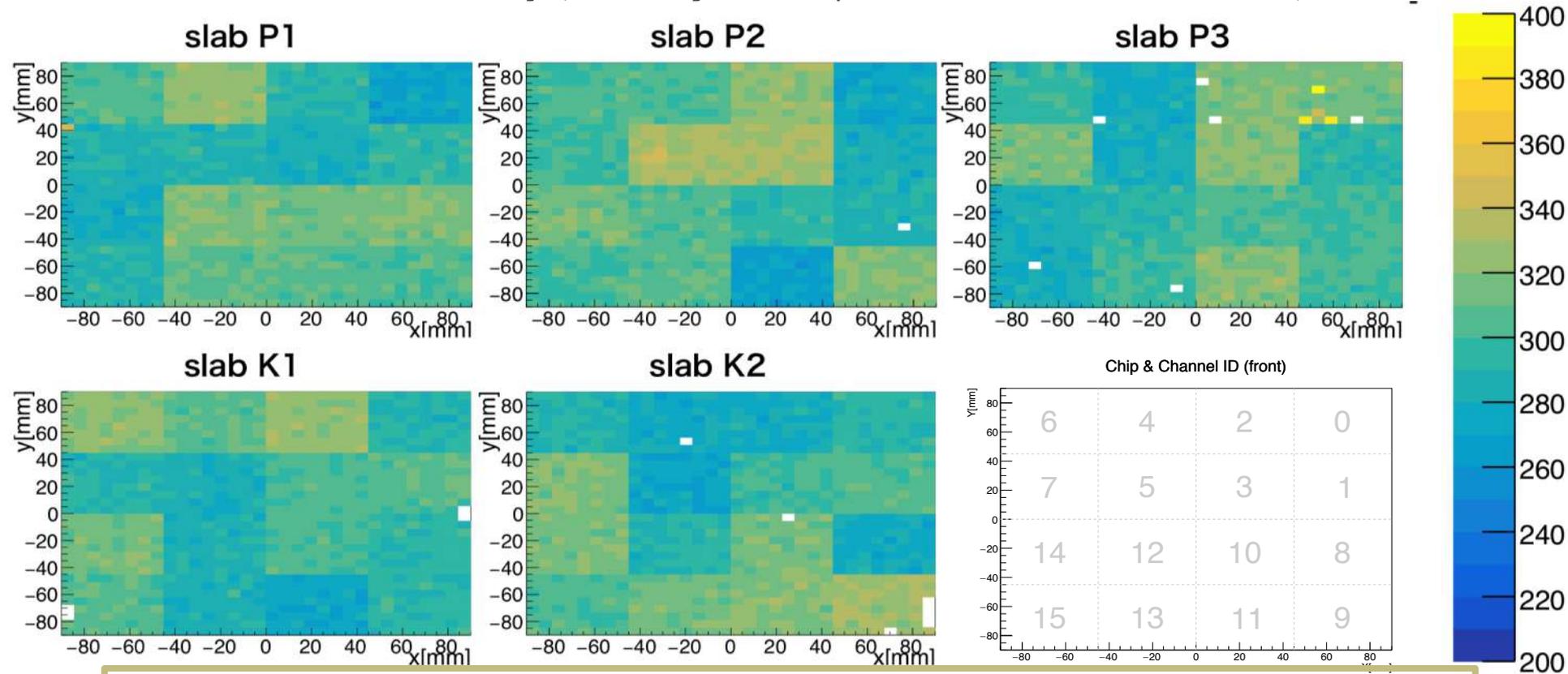
> Although there are differences between chips,
> mean of pedestals looks generally uniform within the same chip.

Pedestal Uniformity: Width

- Sigma of Gaussian
- Result of 1st Memory (Memory-cell dependence is referred later.)
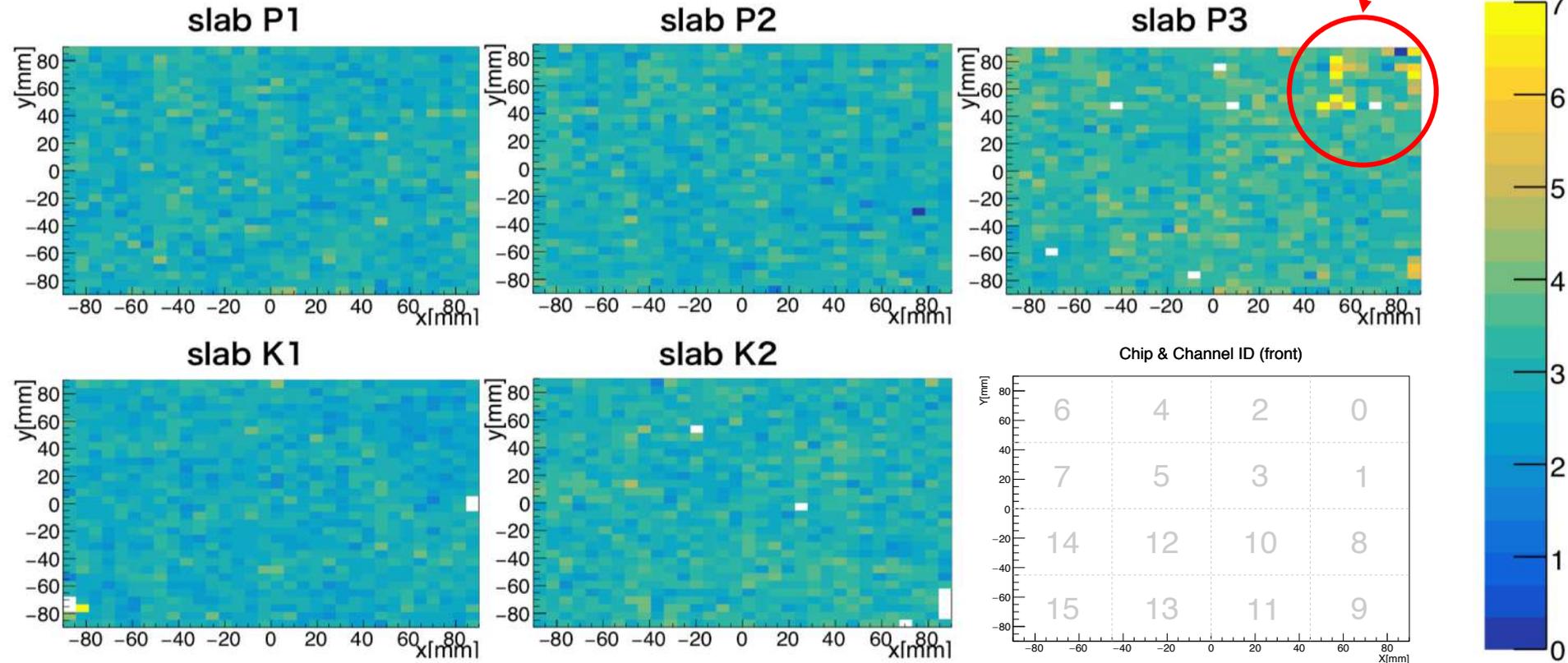
> Width of pedestal is almost uniform (3~4) throughout.

Pedestal Stability

● Pedestal stability is confirmed in this beam time.

Temperature: P1

Pedestal mean: P1 chip0
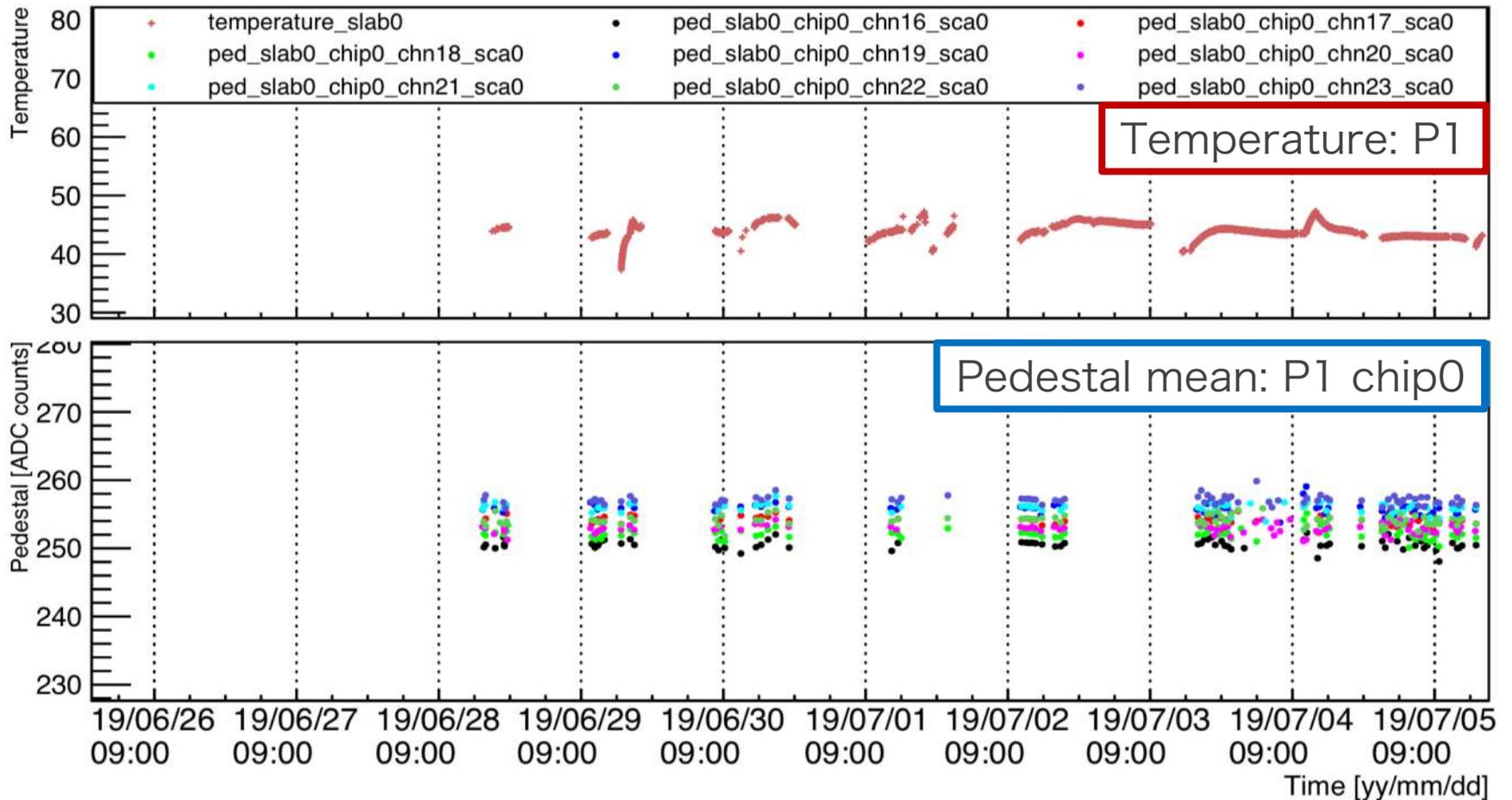
MIP event

- MIP program is performed for mainly energy calibration of all the pixels.
- Hit map: Sum of the triggered events
- Event display: ADC output of single event after event building

➢ Electron energy: 3 GeV

hit map

event display

ADC

P3
(320 μm)
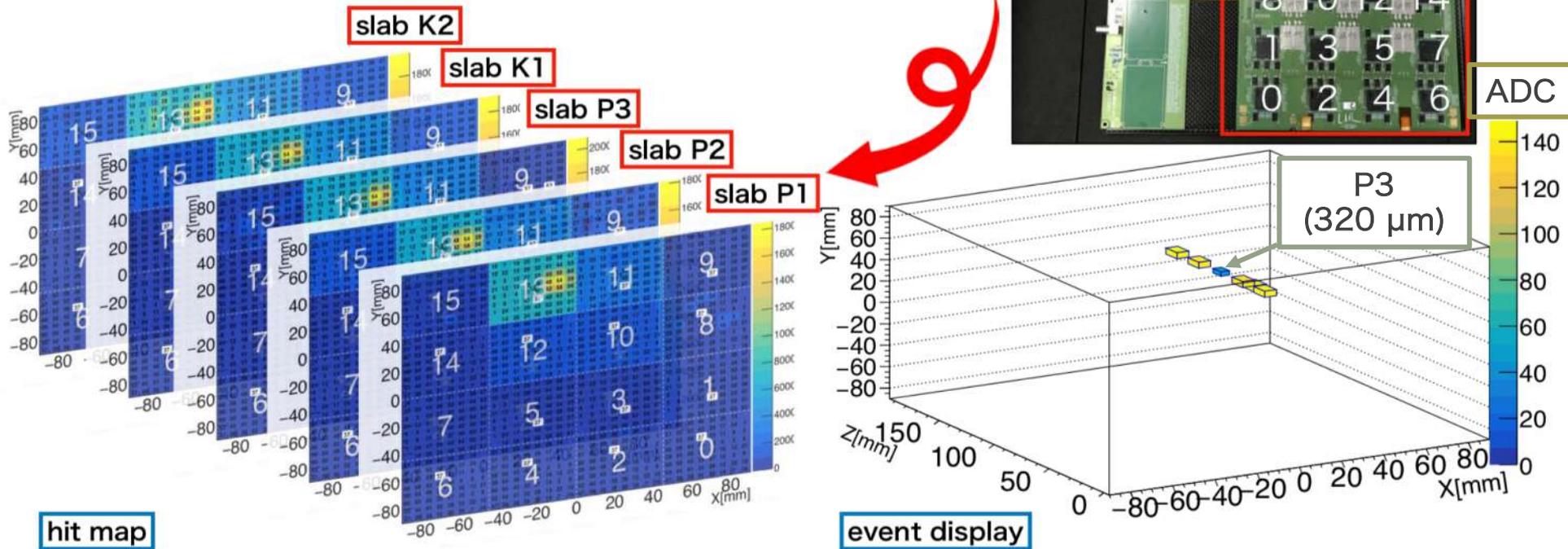
MIP spectrum

- Typical MIP spectrums of each slabs are shown.

- Pedestal is subtracted.

- Fitted by Lan-Gaus function.
  ◦ Convolution of Landau × Gaussian

- MPV: Most Probable Value

- Definition of S/N$_{ADC}$:

$$S/N_{ADC} \equiv \frac{MPV_{1\mathrm{MIP}}}{Width_{pedestal}}$$
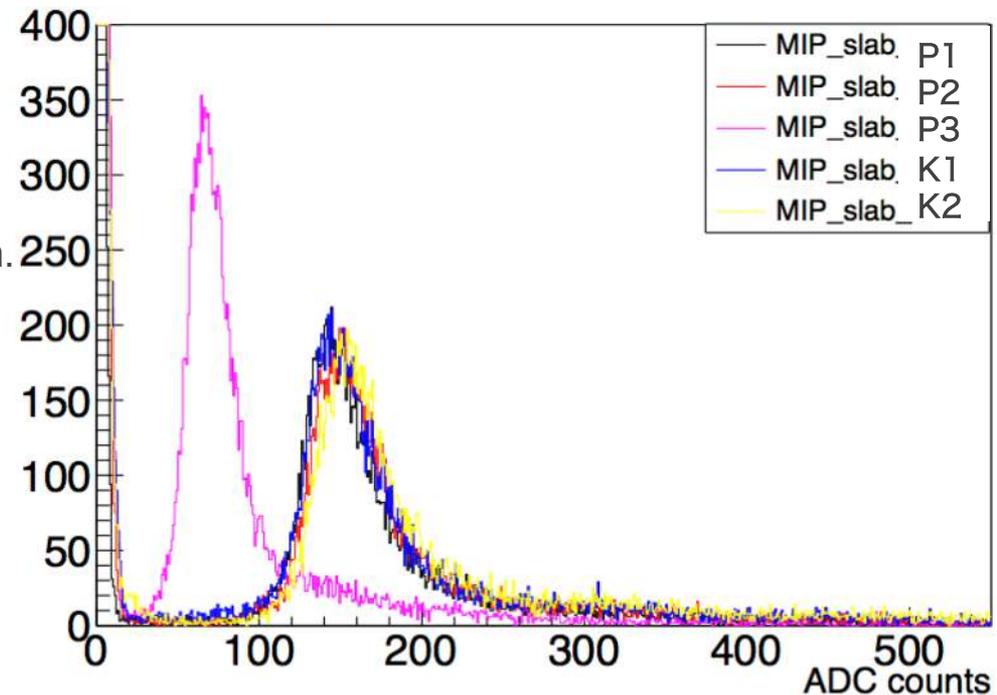
slab	P1	P2	P3	K1	K2
thickness	650μm	650μm	320μm	650μm	650μm
MPV	146.5	144.9	71.3	141.4	146.1
Ped_width	3.0	3.0	3.3	2.8	3.1
S/N	49.0	48.9	21.7	50.2	47.5

MIP calibration

- MPV maps:

MIP calibration

- slab: P1

MPV

Error of MPV

χ^2/ndf

Chip0 is broken?

entries

MPV
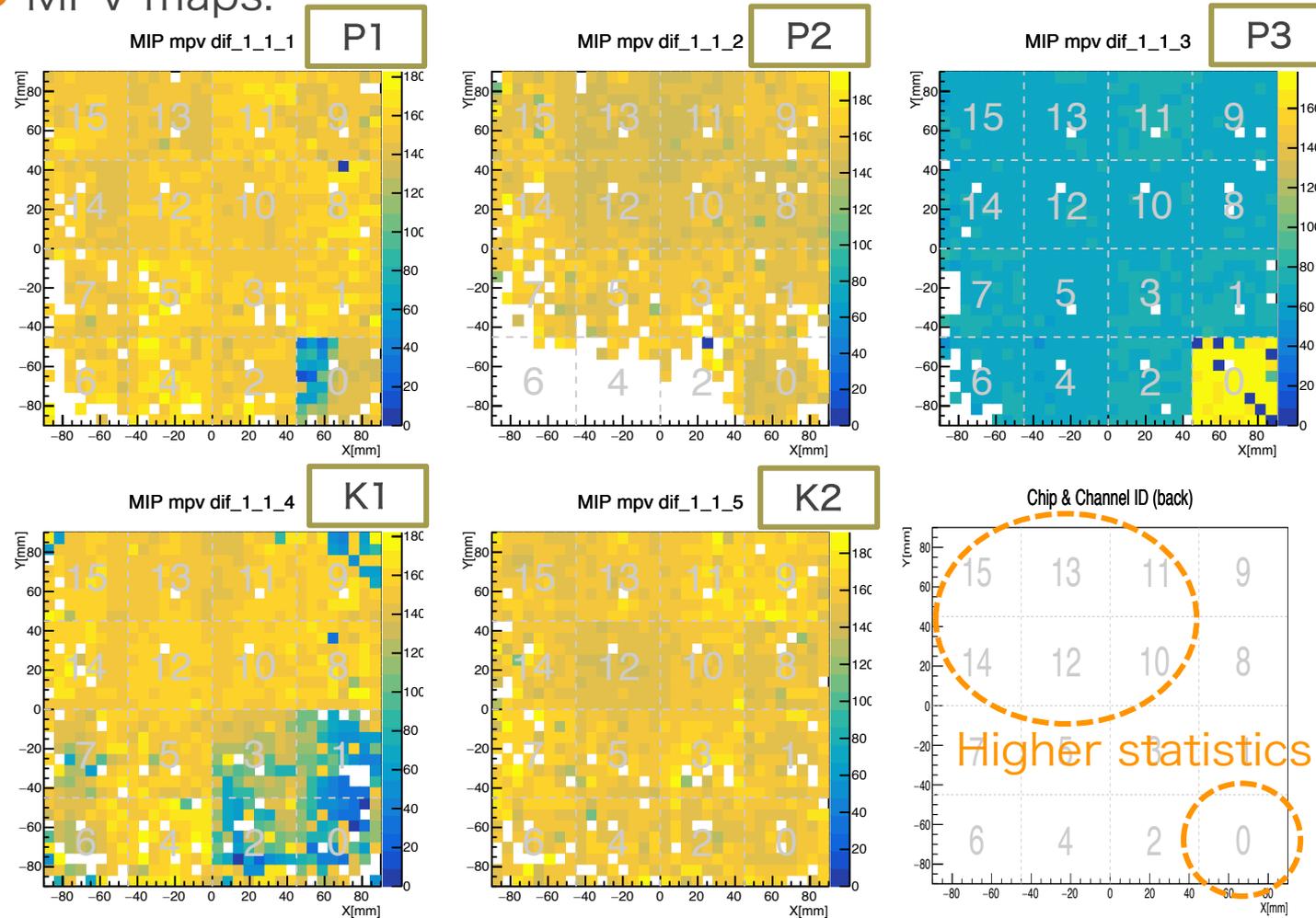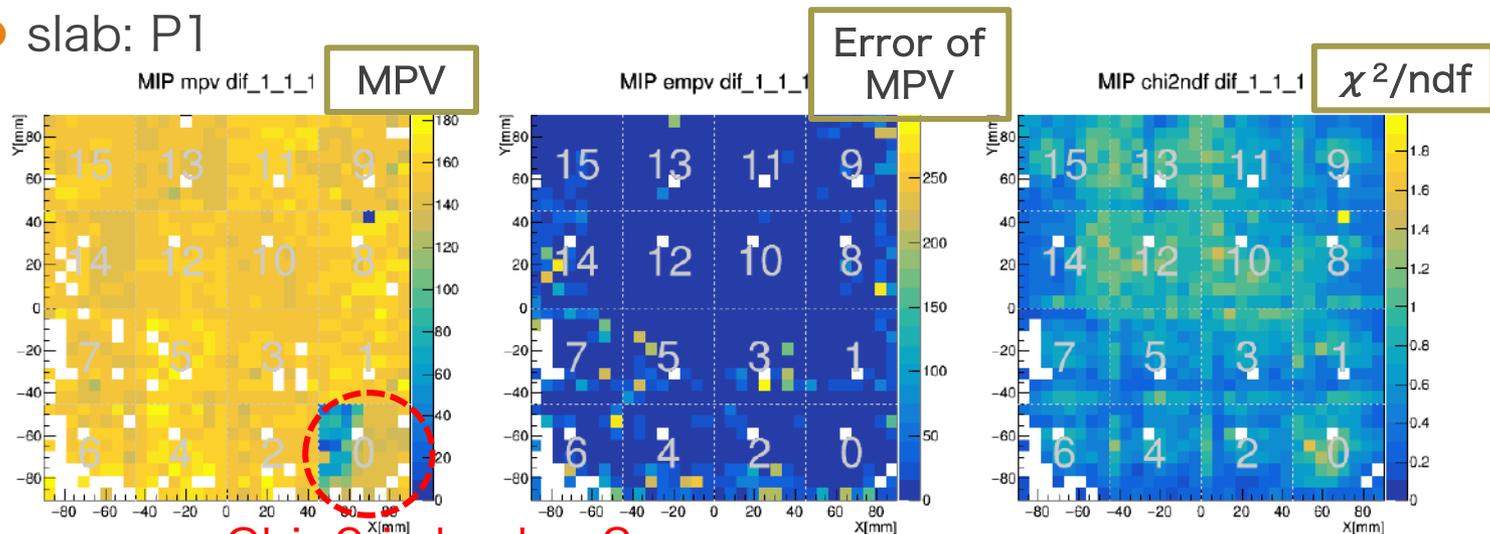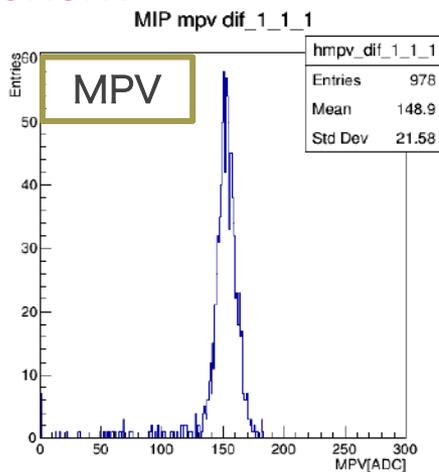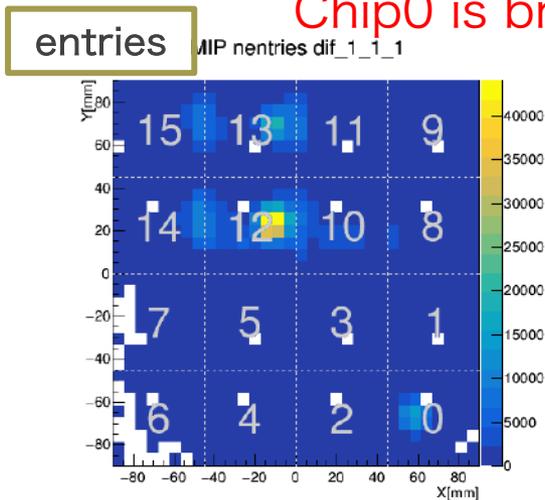
Preliminary

MIP calibration

- slab: P2

MPV

Error of MPV

χ^2/ndf

entries

MPV
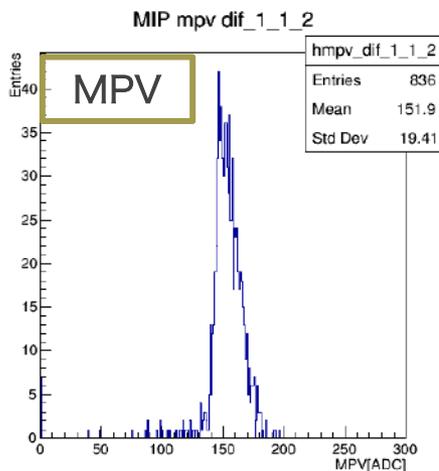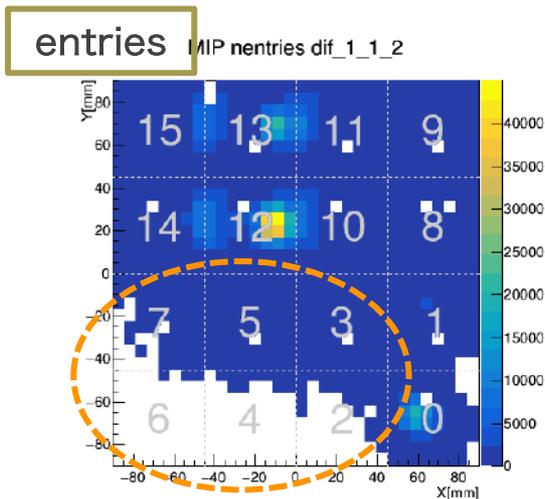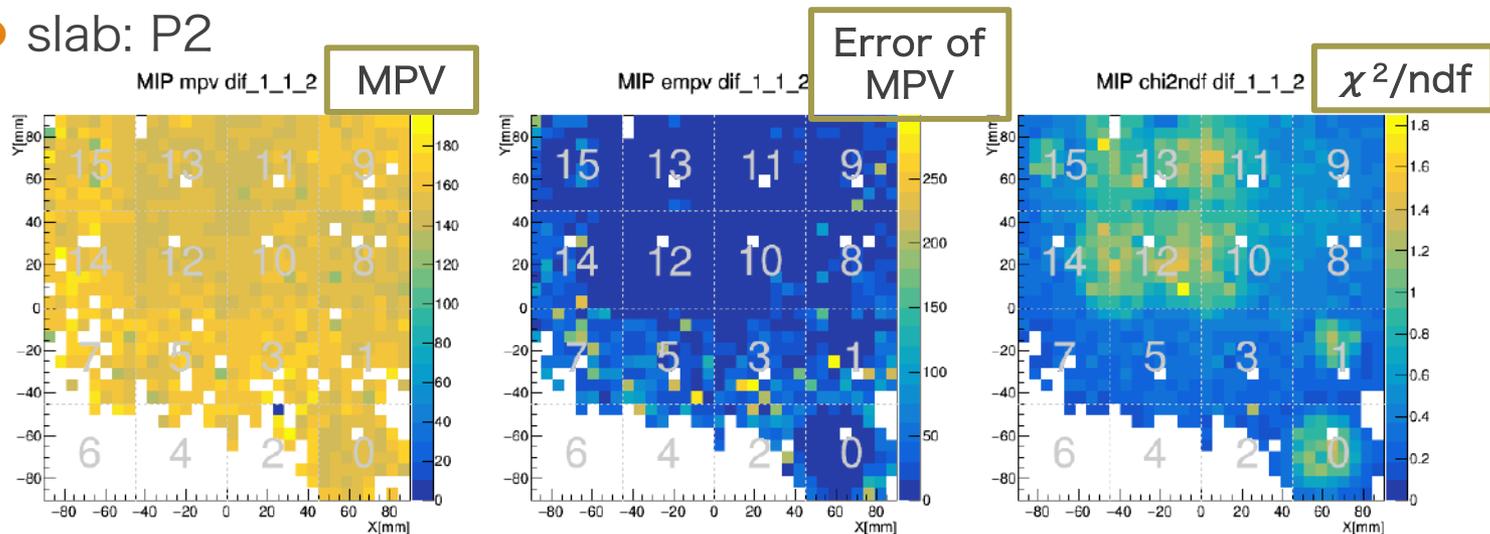
Low-statistics because
DIF was broken in position scan

Preliminary

MIP calibration

- slab: P3
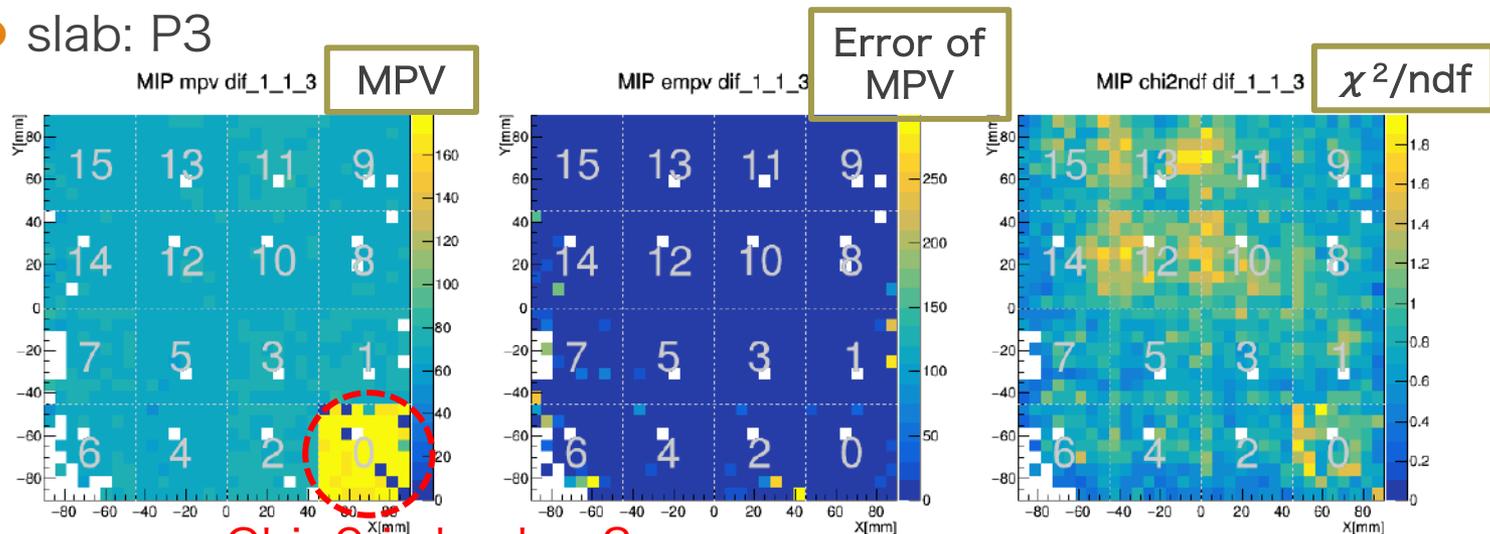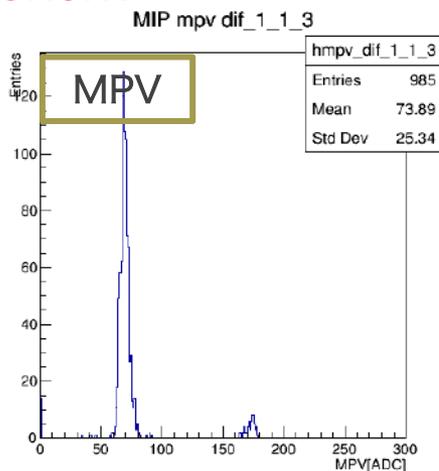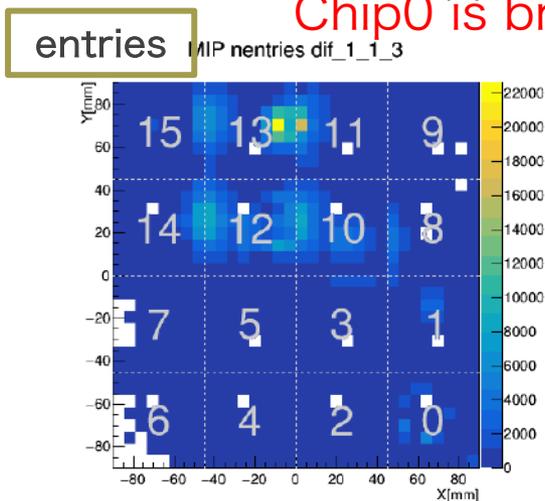
MIP calibration

- slab: K1

MPV

Error of MPV

χ^2/ndf

entries

MPV

HV connection is bad?

Preliminary

MIP calibration

- slab: K2

MPV

Error of MPV

χ^2/ndf

entries

MPV
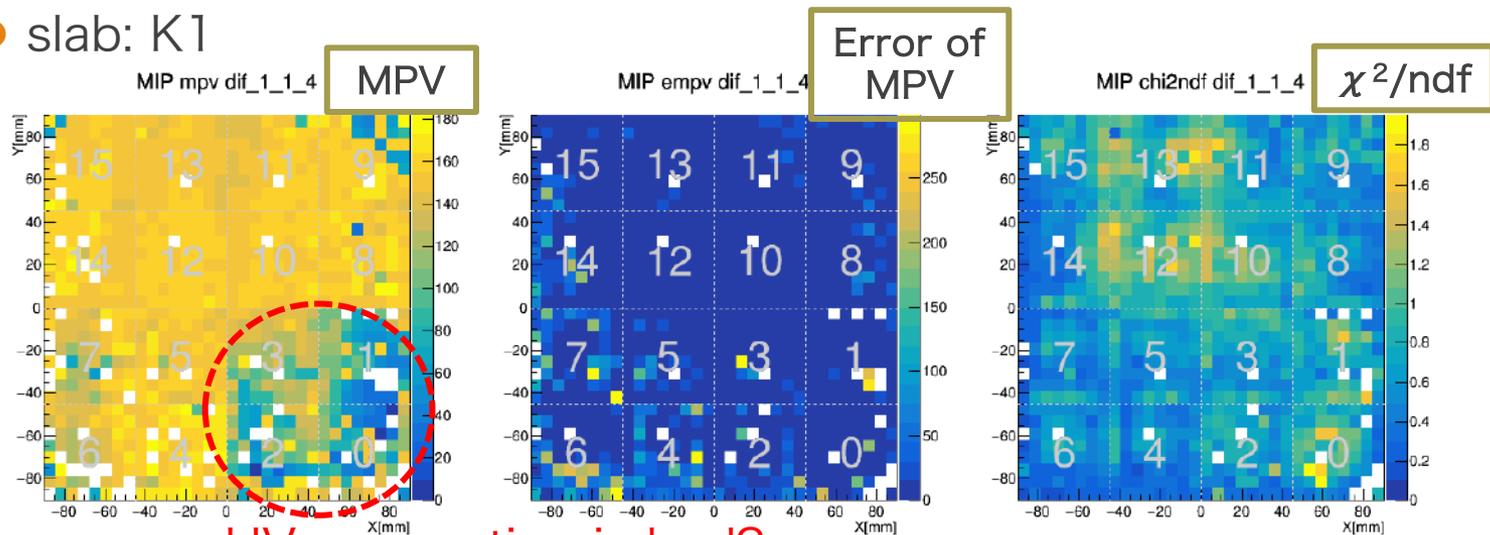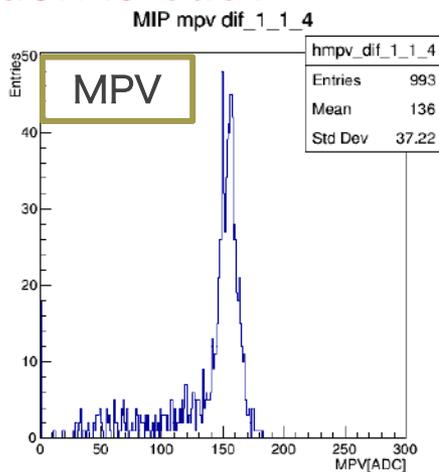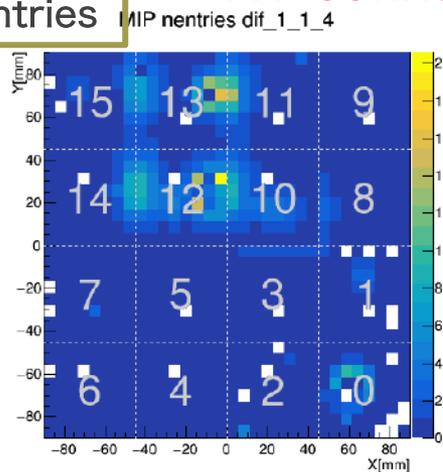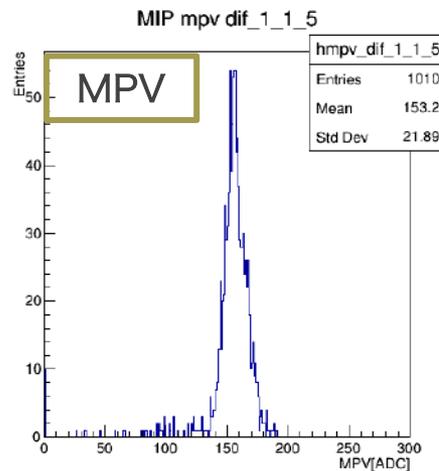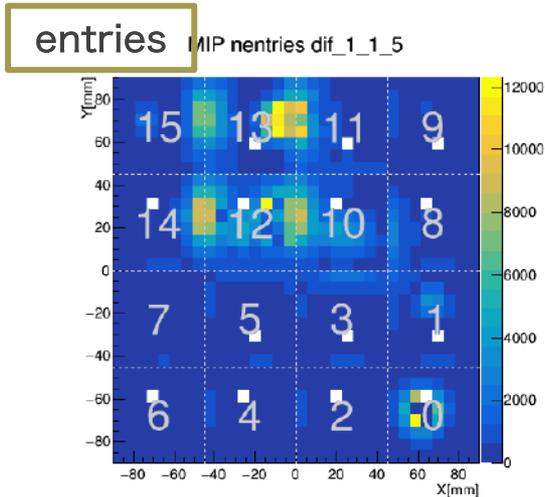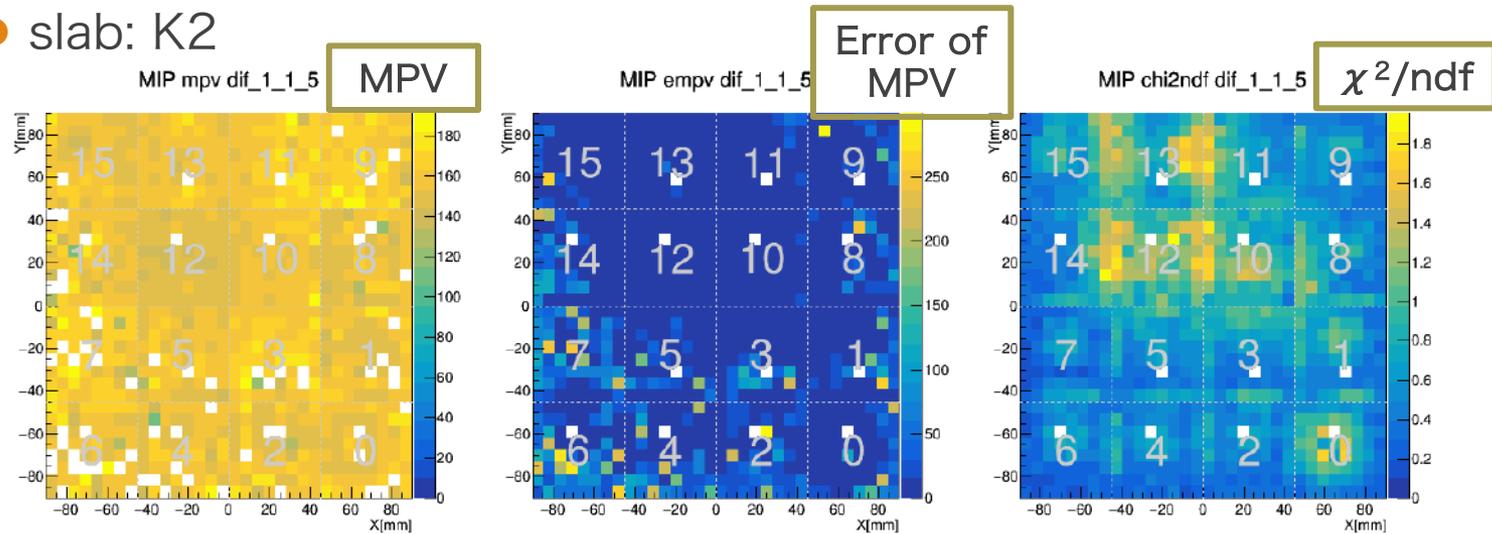
Good!

Preliminary

# MIP calibration: Summary

- MPV maps:
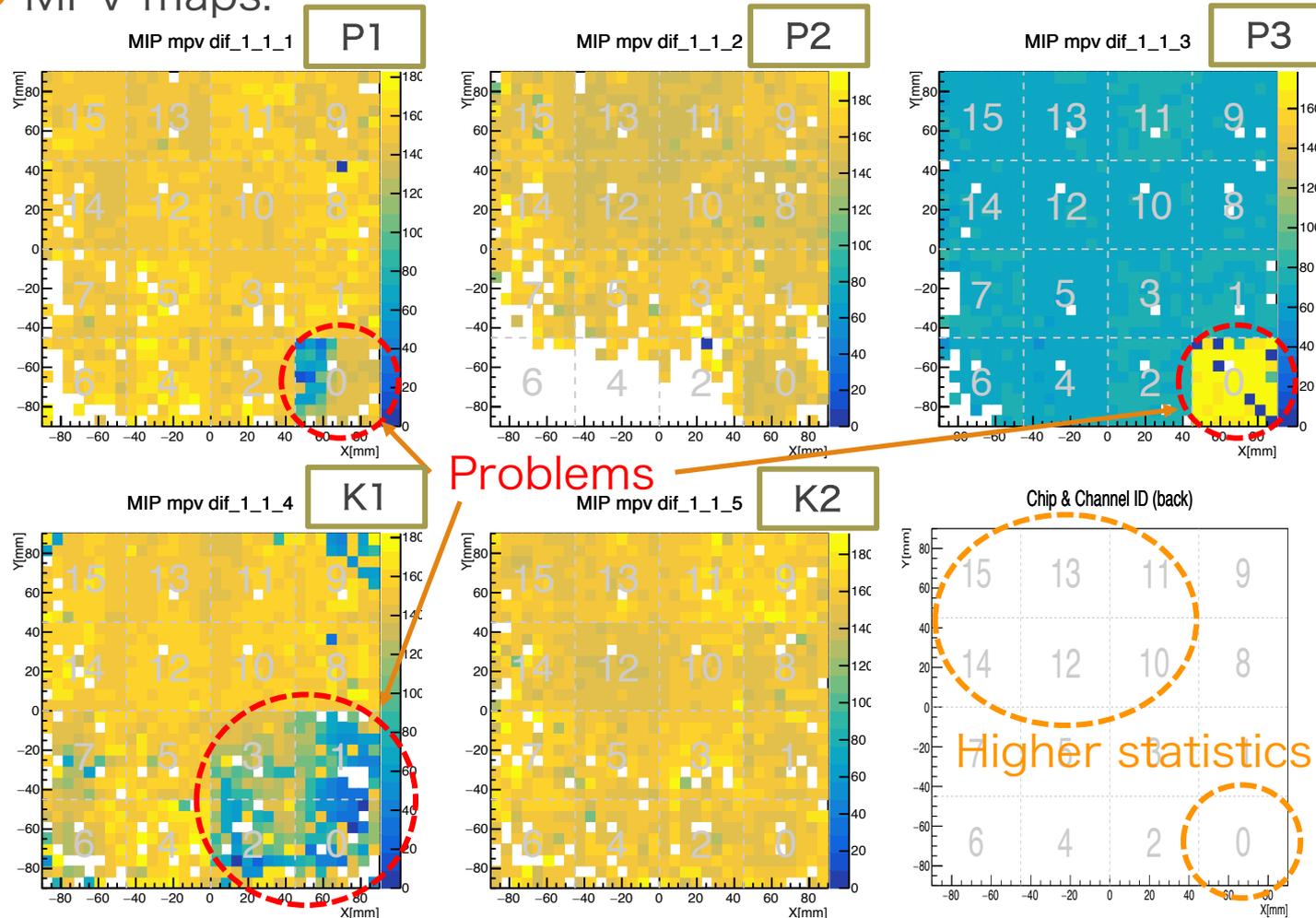
Shower event

- Using the preceding results, we can finally build events.
  - BCID offsets between SLB-based and DIF-based are corrected.

- A typical event is checked with event display.
  - In this picture, color scale is not converted to energy, still ADC output.

Event display of shower event
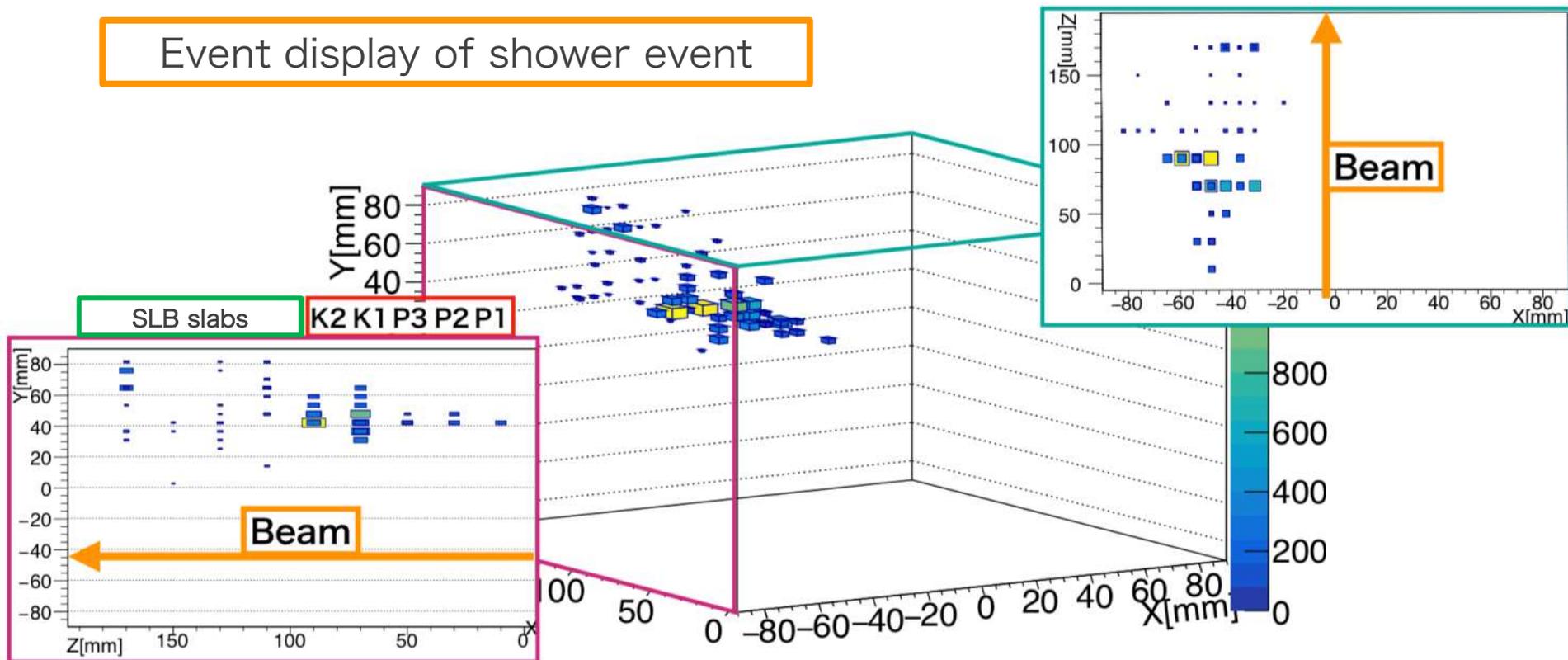
Shower Analysis: Hit Energy

● Hit energy after MIP calibration (run_42003)

Single cell hit energy in 3 GeV e⁻ beam
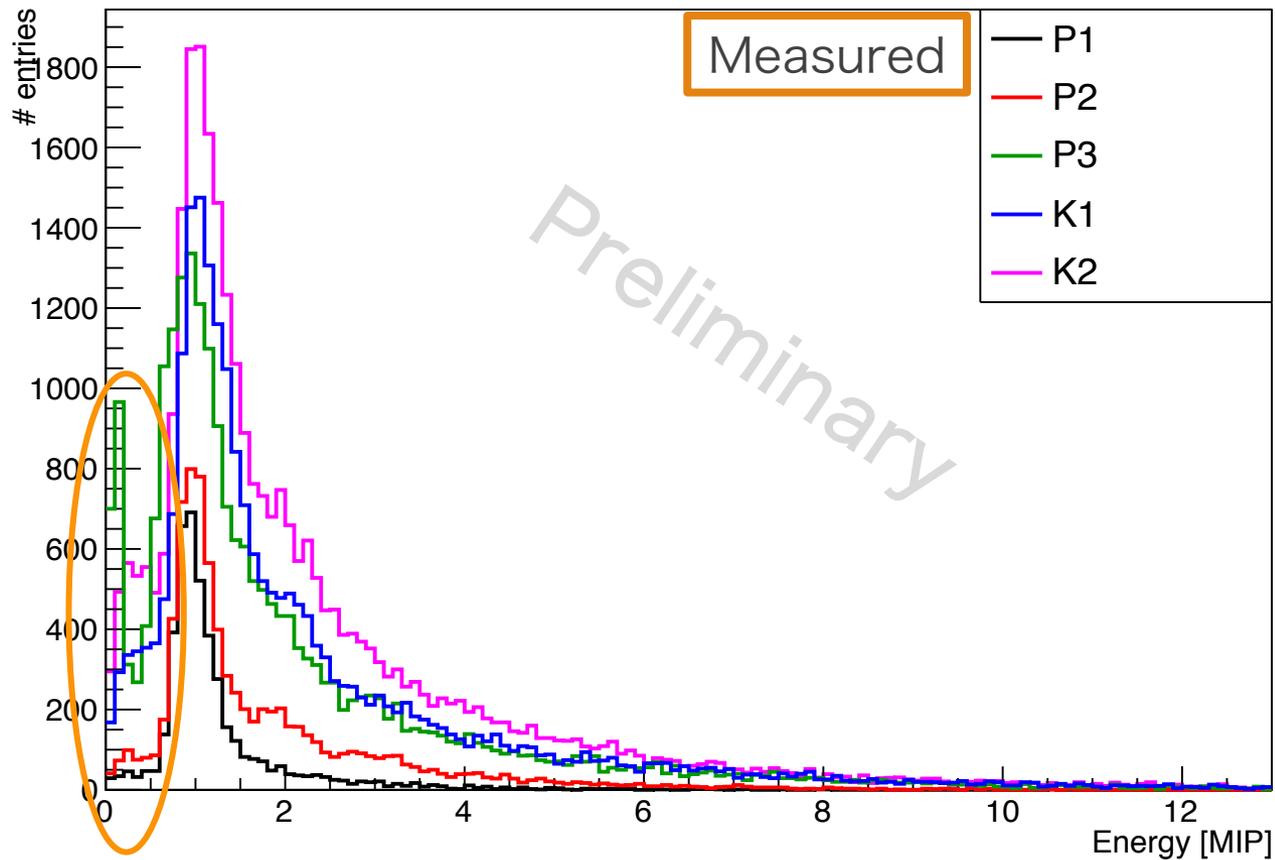
Simulation

- We performed detector simulation for this beam test.

- Simulator: DDSim in iLCSoft

- Structure of FEV13-Jp:
  - CF: 0.6mm
  - Electronics(Air)
  - PCB: K1: 1.6mm, others: 1.8mm
  - Glue(Air): 0.08mm
  - Si: 0.32mm or 0.65mm
  - Glue(Air): 0.08mm
  - Kapton(Cu): 0.06mm
  - CF: 0.6mm
  - Plastic(polyethylene): 5mm

Hit Energy conf0_e_3GeV — w/o Tungsten

hiten_conf0_e_3GeV_0	
Entries	10087
Mean	0.2513
Std Dev	0.1267

Legend: P1, P2, P3, K1, K2

Hit Energy conf1_e_3GeV — w/ Tungsten

| hiten_conf1_e_3GeV_0	
Entries	10663
Mean	0.2532
Std Dev	0.1383
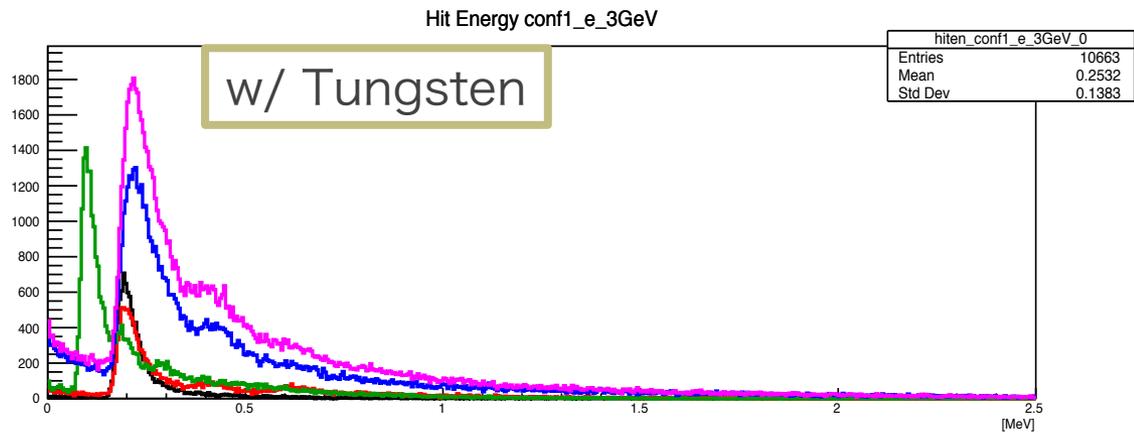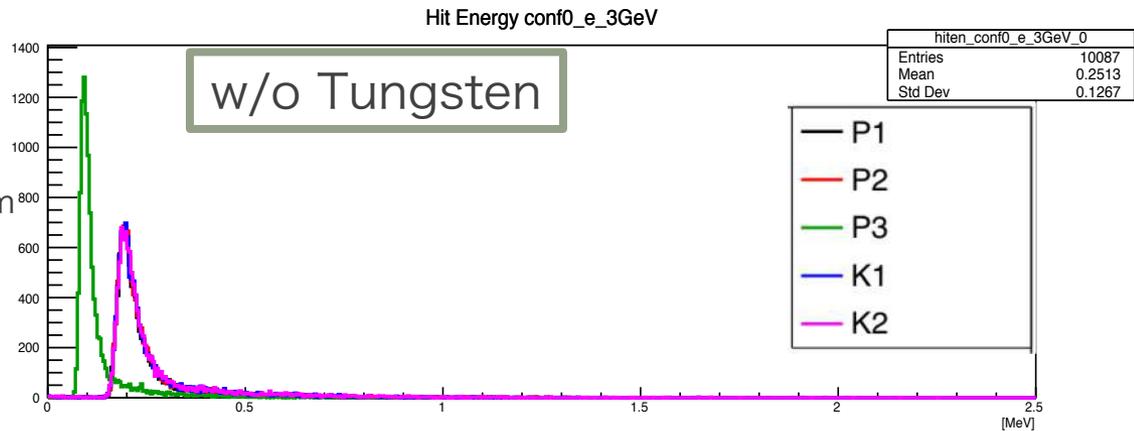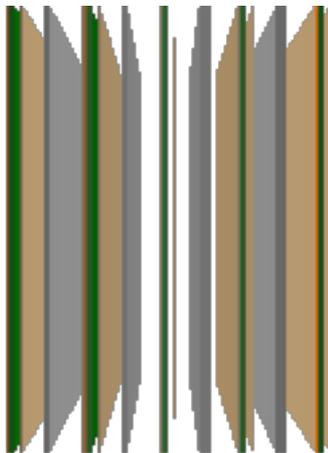
Comparison of Measured and Simulated.

- Simulated results are converted to MIP units and compared to measured ones.

- Work in progress.

Single cell hit energy in 3 GeV e⁻ beam

Hit Energy conf1_e_3GeV
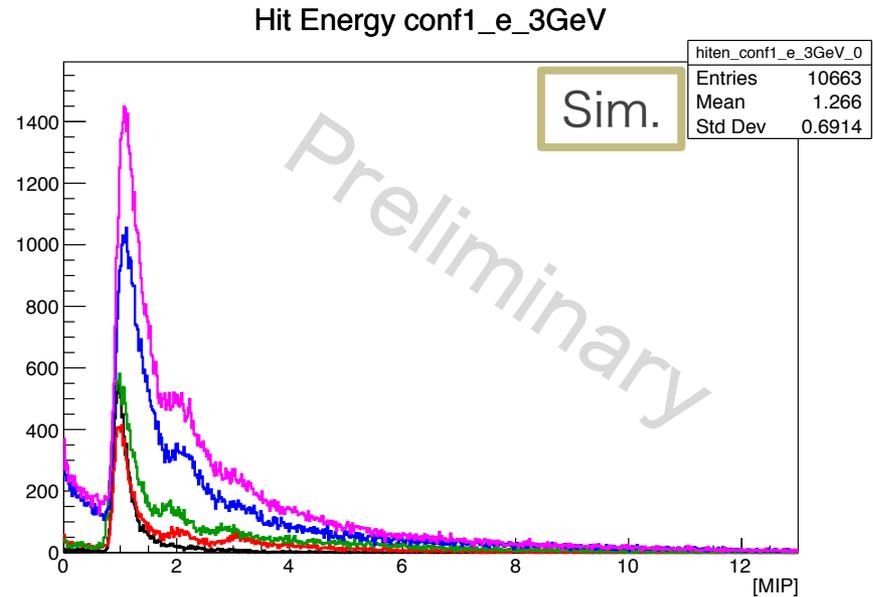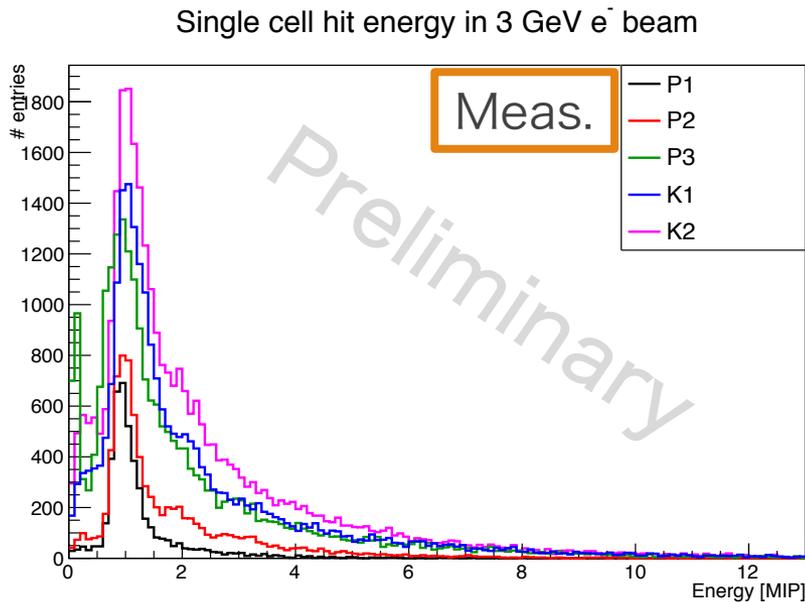
TDC Correlation with MIP
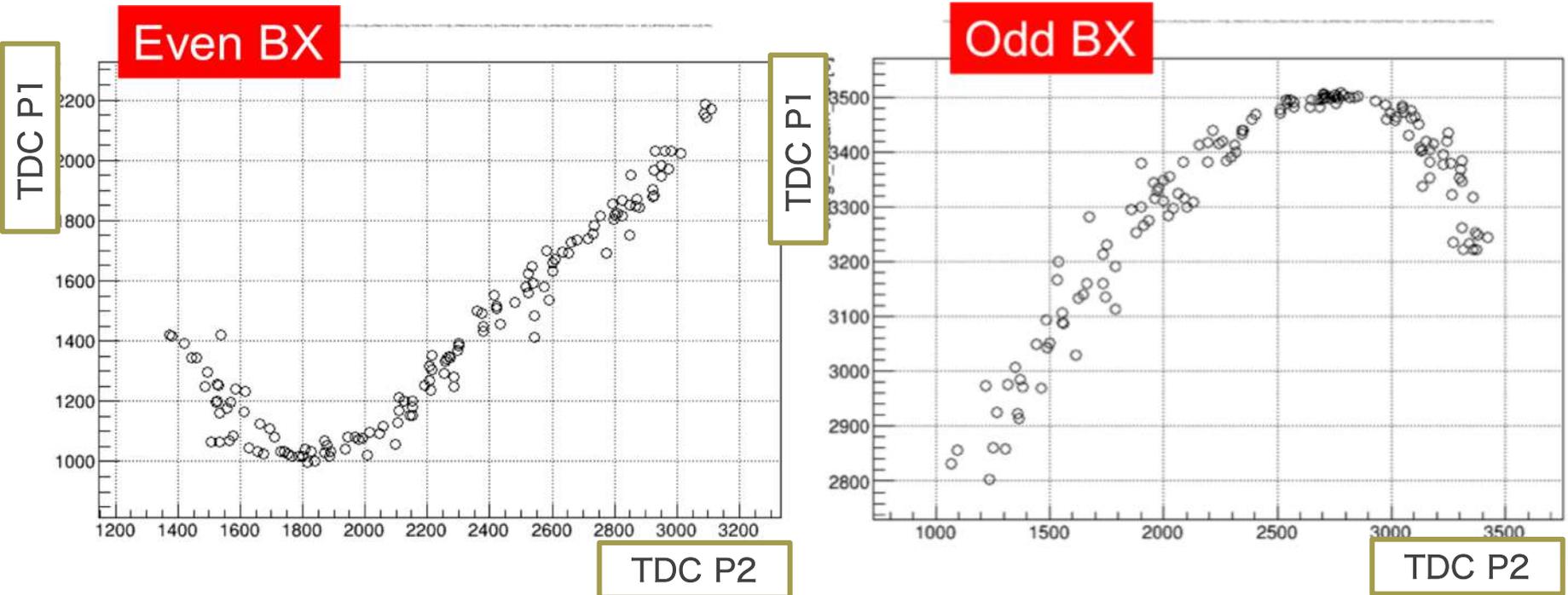
- Correlation of TDC between slab P1 and P2
- Select 1 ch (at the center of the beam), 450 < ADC < 500 (to avoid time-walk)
- ~10 / 1 ns at the normal slope: timing resolution ~ a few ns?
- TDC calibration in progress.

Correction of Time Walk

Very Preliminary

- Time Walk: TDC dependence on ADC
- TDC-interval vs ADC are fitted by Log function.
- Width of TDC-interval is improved: 117 → 52.

timing resolution:
5.2 ± 1.6 ns
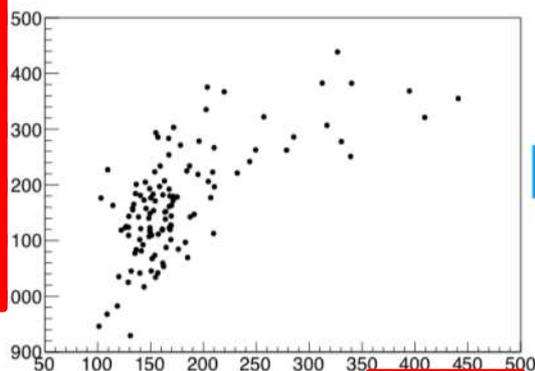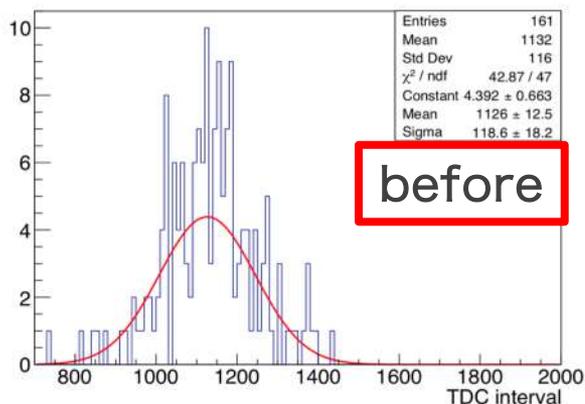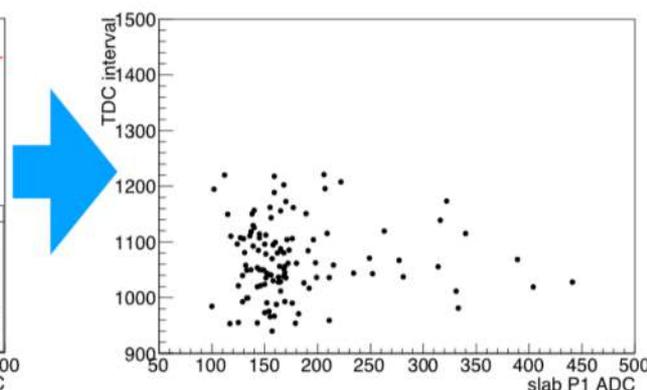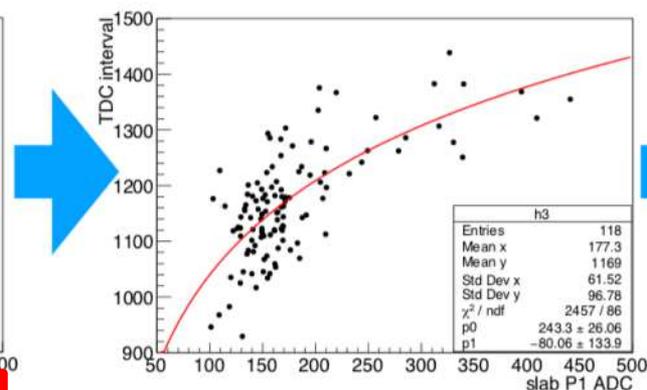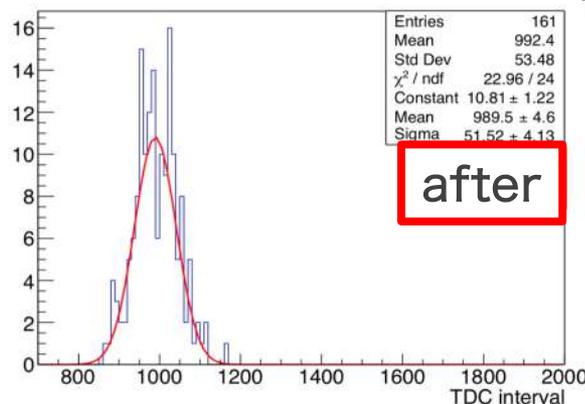
from previous talk,
- TDC to real time calibration factors
  - 0.127 ns / TDC count (up)
  - 0.066 ns / TDC count (down)

Remaining Issues

Yu Kato, LCWS2019

Double pedestal / Retrigger

- run 32015, slab P1

All   Good   Retrigger

Mean

Width

Hip map   Mean difference   entry ratio
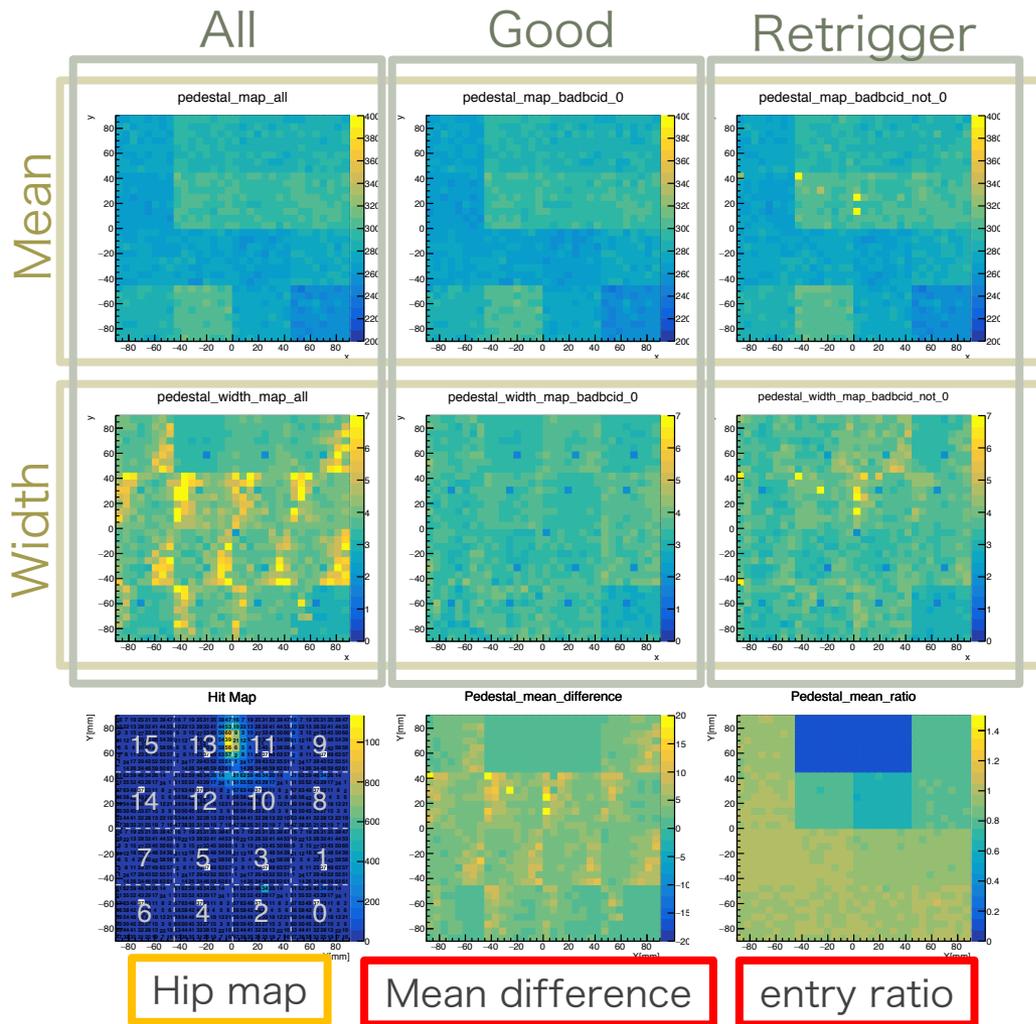
Retrigger event:
BCID is consecutive.
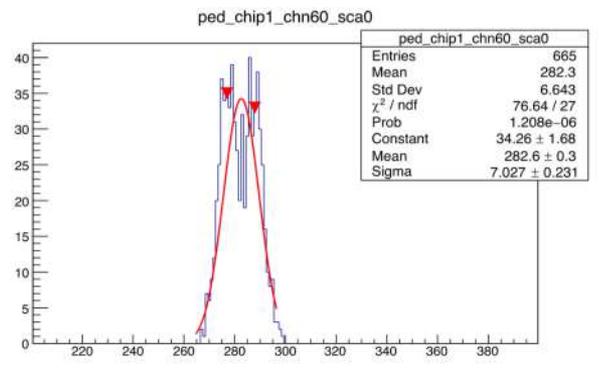
Double pedestal
by retrigger

Pedestal difference between ADC/TDC mode

- We found the difference of pedestals between ADC/TDC mode.
- Memory-cell dependence is not same.
- In the first memory cell, the difference of typical Ped_mean is ~15.
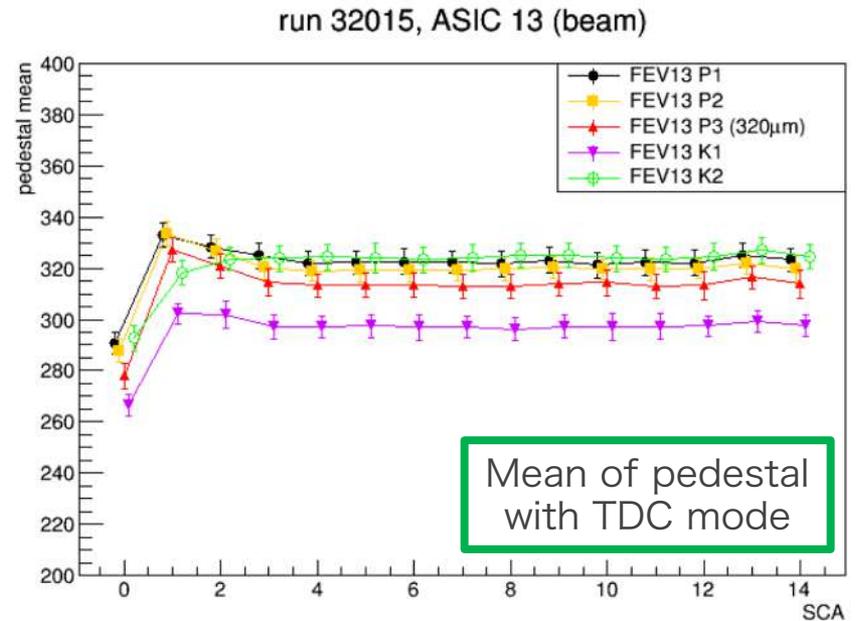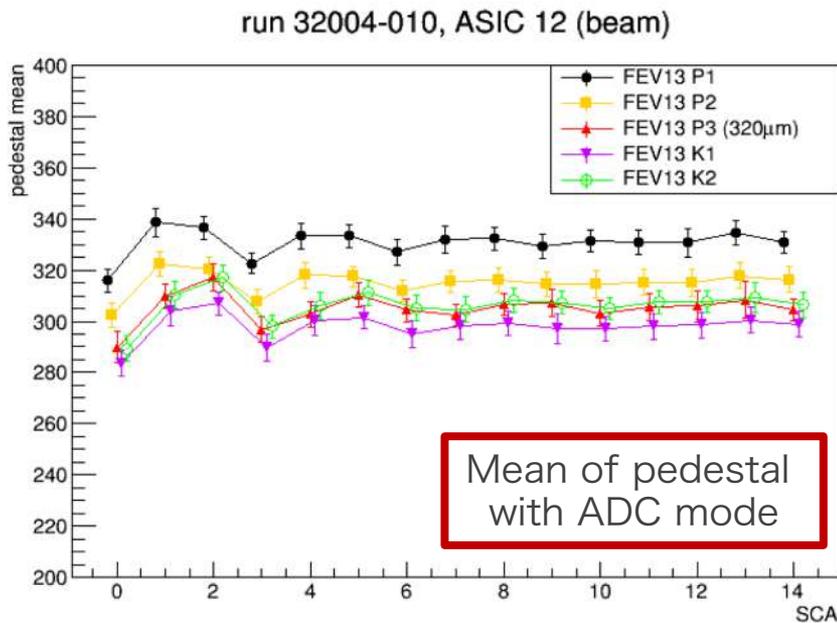
Mean of pedestal with ADC mode

Mean of pedestal with TDC mode

Pedestal difference between ADC/TDC mode

- We found the difference of pedestals between ADC/TDC mode.
- Memory-cell dependence is not same.
- In TDC mode, SCA~2 is worse.
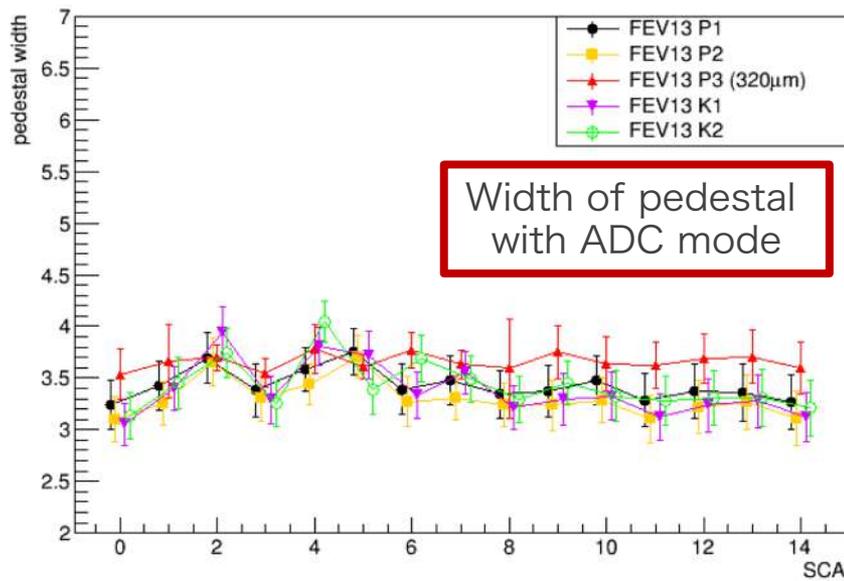
Pedestal difference between ADC/TDC mode
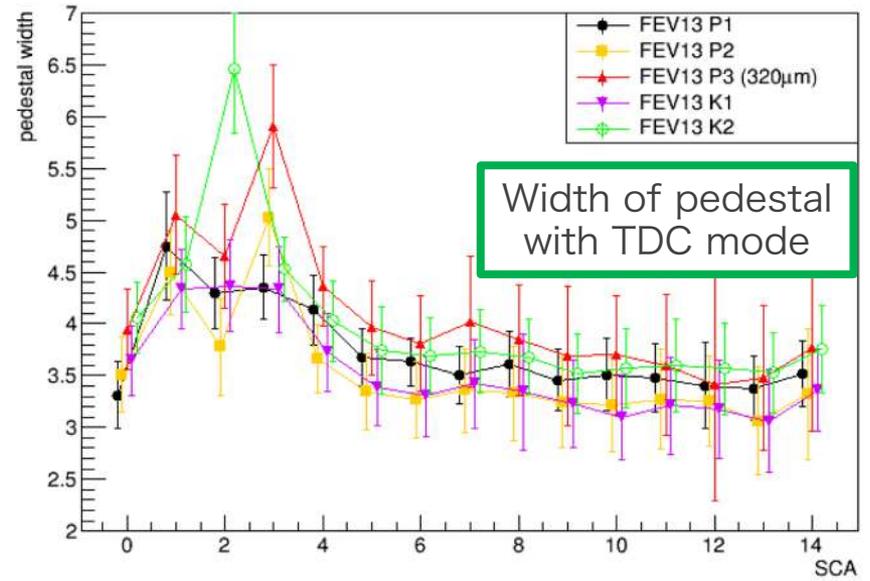
- We found the difference of pedestals between ADC/TDC mode.
- Memory-cell dependence is not same.
- In TDC mode, SCA~2 is worse.

Width of pedestal with TDC mode
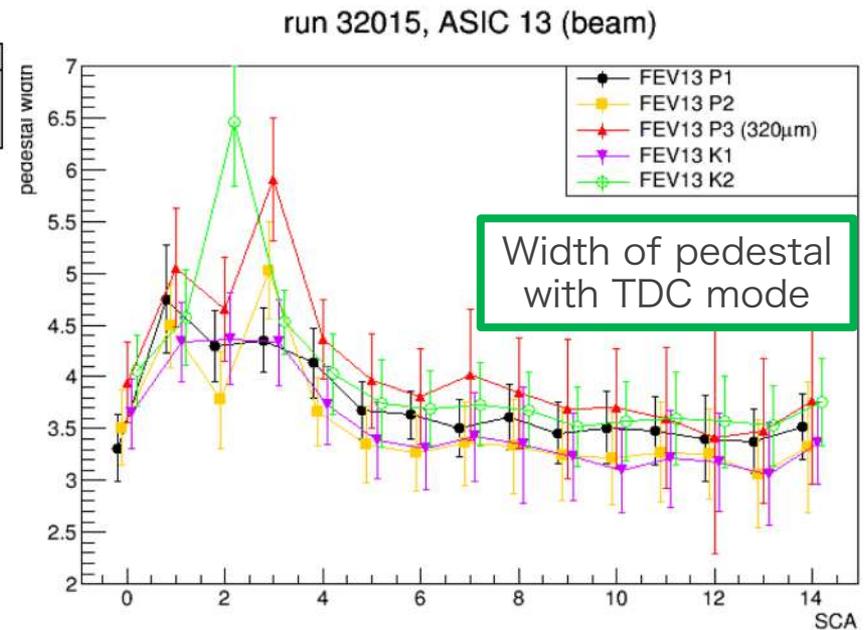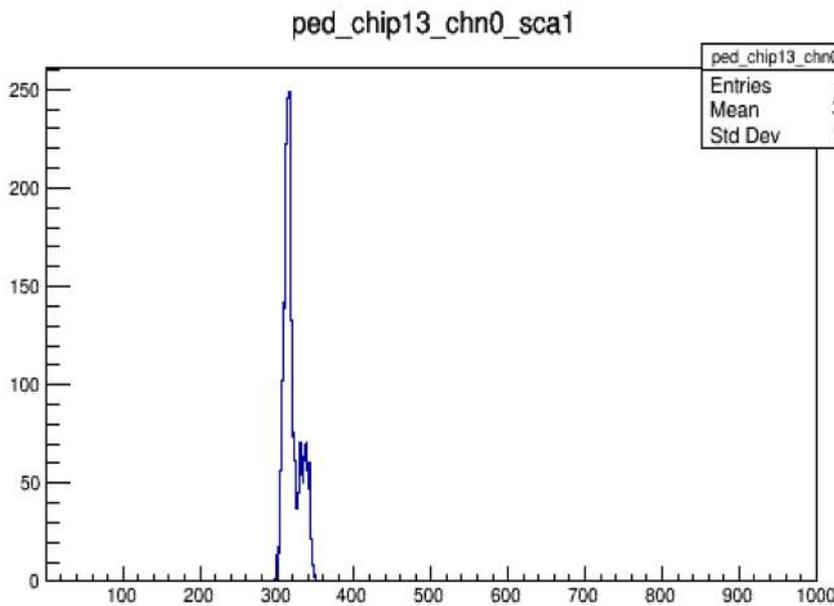
➢ There are double pedestal even after bcid selection in TDC mode.
➢ The criteria for identification of double pedestal is not optimized.

Work in progress.

Summary

- FEV13-Jp: 5 slabs from Kyushu U.

- BT 2019 DESY: **All the slabs worked consistently.**

- Pedestal study
  - Uniformity and Stability is verified.

- MIP calibration
  - MIP calibration is almost completed.
  - S/N is obtained for 5 slabs:

slab	P1	P2	P3	K1	K2
thickness	650μm	650μm	320μm	650μm	650μm
S/N$_{ADC}$	49.0	48.9	21.7	50.2	47.5

- Shower analysis
  - Event building has done and shower event is seen in event display.
  - We take a look at hit energy which is consistent with simulation result.
  - Work in progress.

- TDC test
  - Time walk is corrected, but very preliminary.
  - Timing resolution is obtained, however we need more detail study using injection.

- Several issues remain:
  - Retriggered events are removed practically although the cause is still unknown.
 - In TDC mode, pedestals become worse because of retriggers.

backup

R&D of SiW-ECAL technological prototypes

ASU: 12 years of R&D

Most complex element: electro-mechanical integration

- Distrib / Collect signals from VFE (ASICs), Analog & Digital with dyn. range ≥ 7500
- Mechanical placer & holder for Wafers → precision
- Thickness constraints

FEV11

DIF + SMB

ASU equipped with 4 Si-wafers

256 P-I-N diodes
0.25 cm² each
9 x 9 cm² total area

FEV11-COB

FEV13

Vincent.Boudry@in2p3.fr
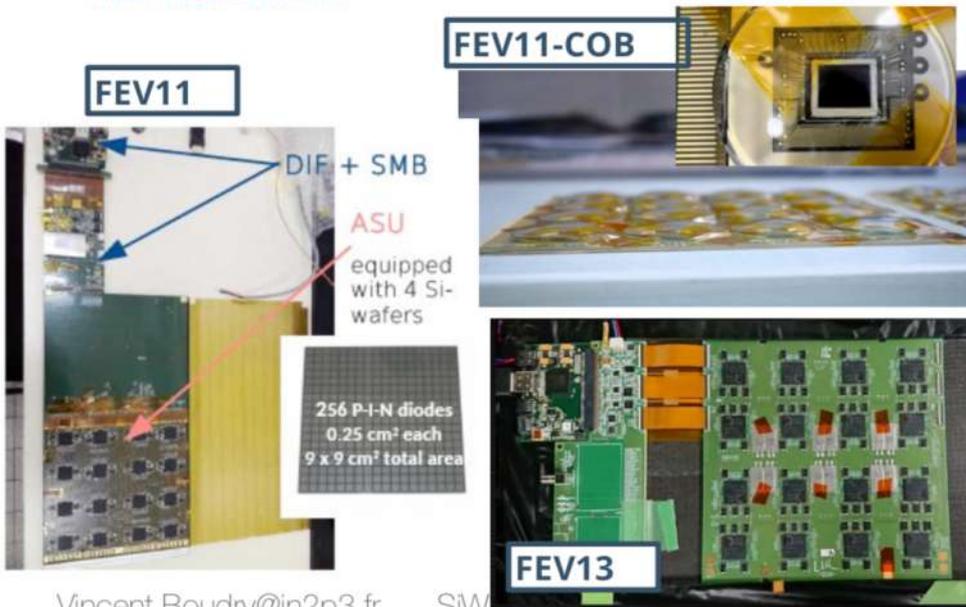
Milestone	Date	Object	Details	REM
1st ASIC proto	**2007**	SK1 on FEV4	36 ch, 5 SCA	proto, lim @ 2000 mips
1st ASIC	2009	SK2	64ch, 15 SCA	3000 mips
1st prototype of a PCB	**2010**	FEV7	8 SK2	COB
1st working PCB	2011	FEV8	16 SK2 (1024 ch)	CIP (QGFP)
1st working ASU in BT	**2012**	FEV8	4 SK2 readout (256ch)	best S/N ~ 14 (HG), no PP retriggers 50–75%
1st run in PP	2013	FEV8-CIP		BGA, PP
1st full ASU	**2015**	FEV10	4 units on test board 1024 channel	S/N ~ 17–18 (High Gain) retrigger ~ 50%
1st SLABs	2016	FEV11	7 units	
pre-calo	**2017**	FEV 11	7 units	S/N ~ 20 (12)$_{Trig.}$ 6–8 % masked
1st technological ECAL	2018	SLABvFEV11 & FEV13 SK2a+ Compact stack	SK2 & SK2a (⊃timing)	Improved S/N Timing...

R&D of SiW-ECAL technological prototypes

Beam-test 2015-2018